

Fig. 1a

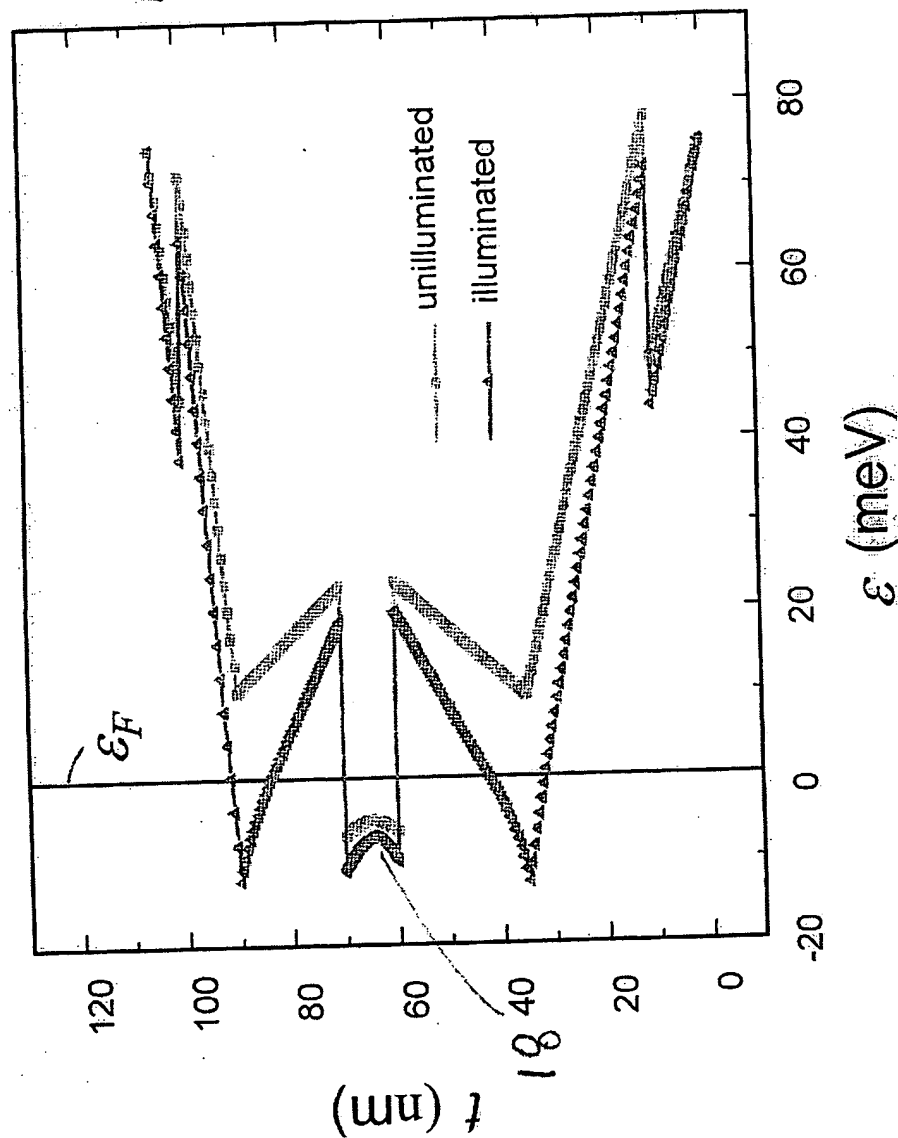
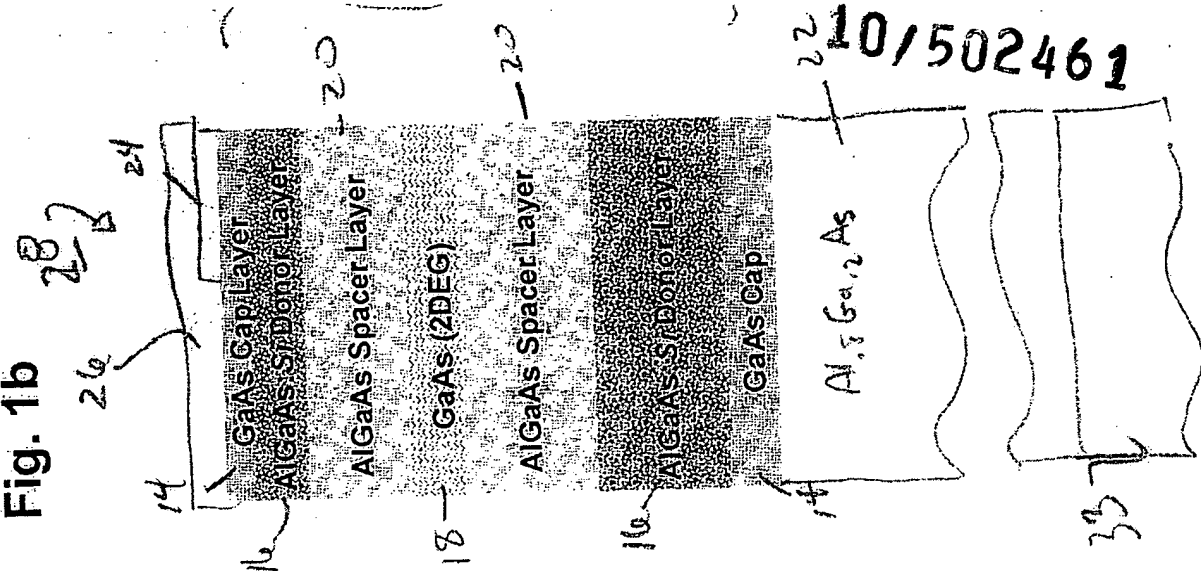


Fig. 1b



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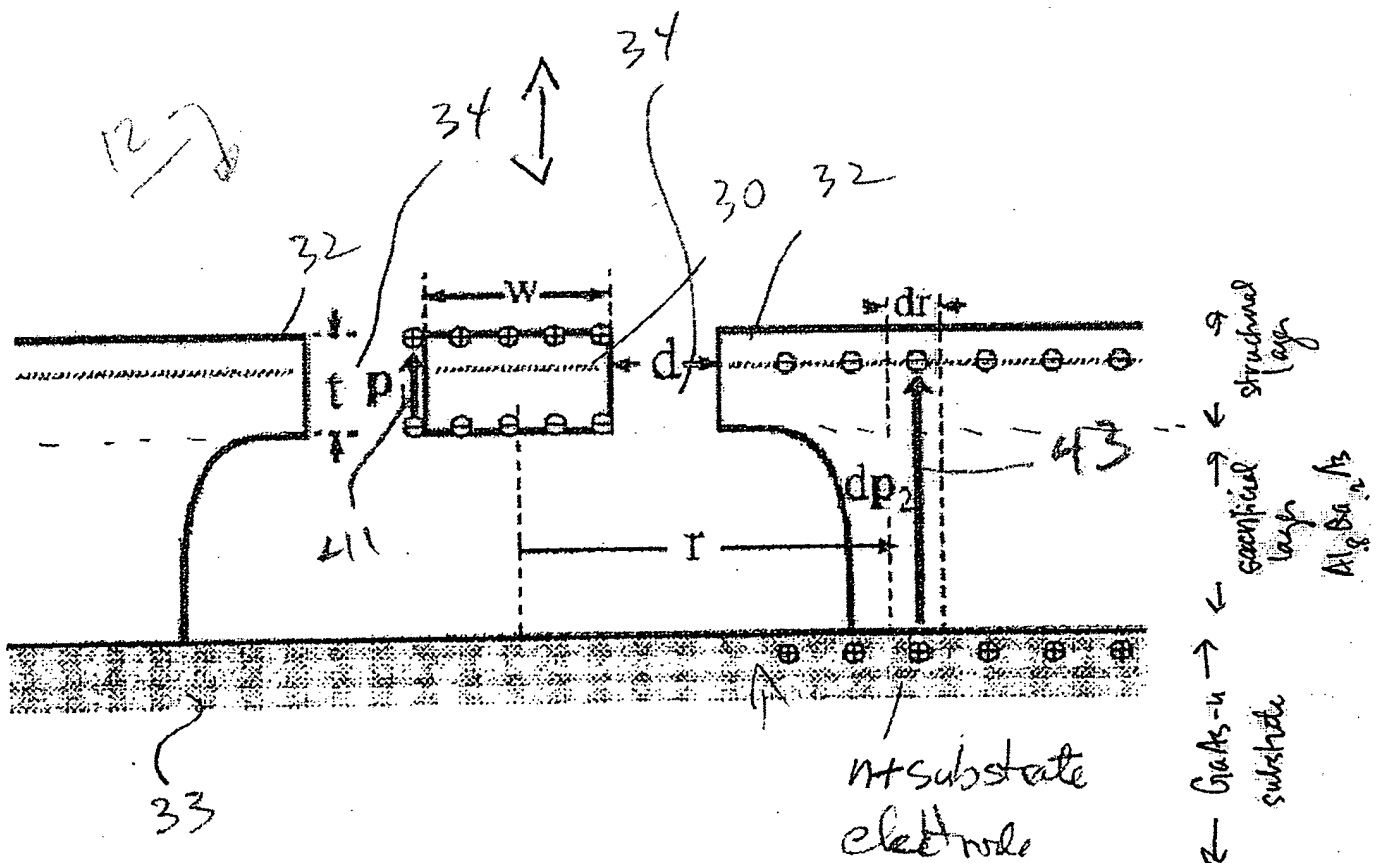


Fig. 2

10/502461

Mid
H

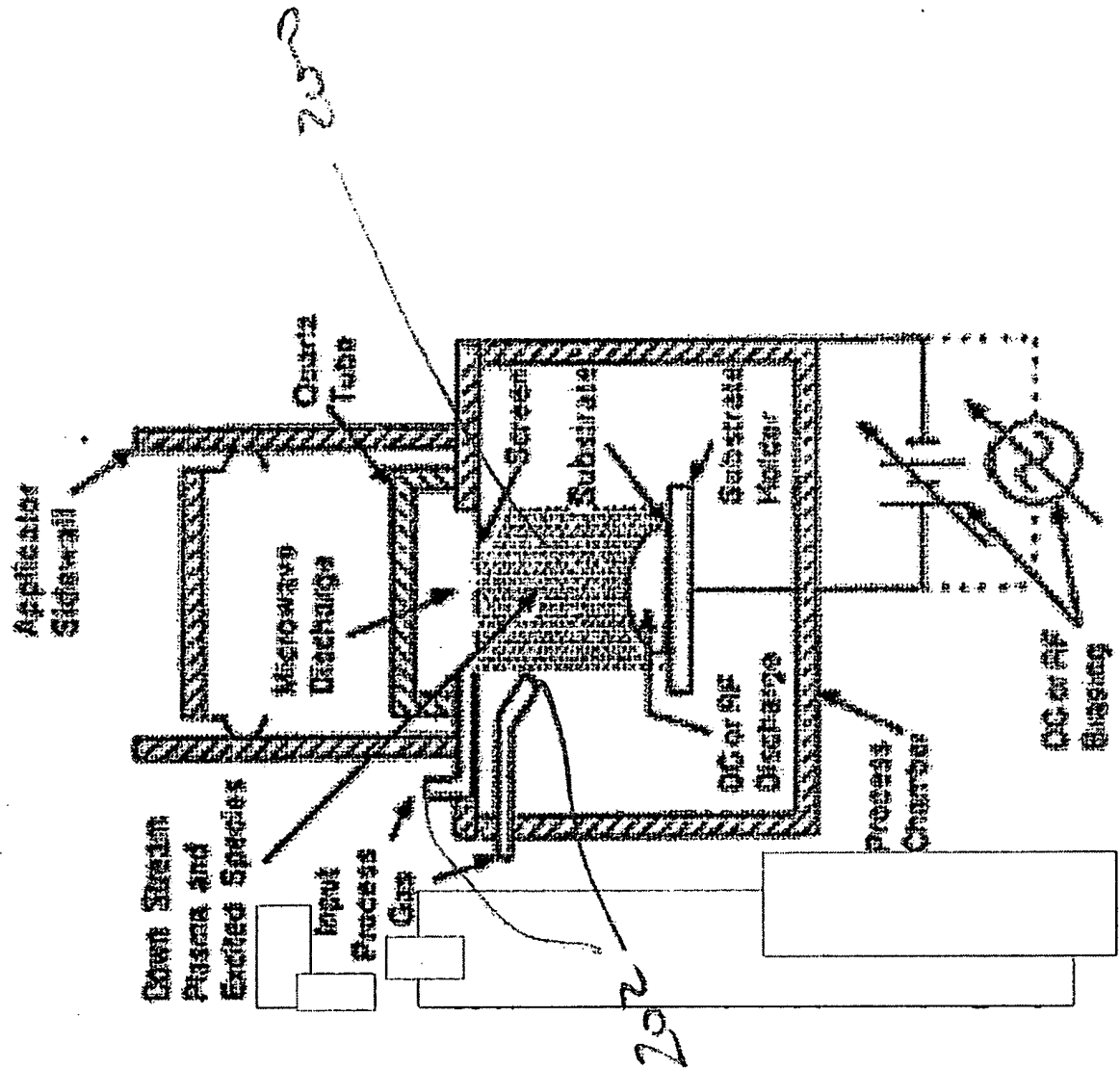
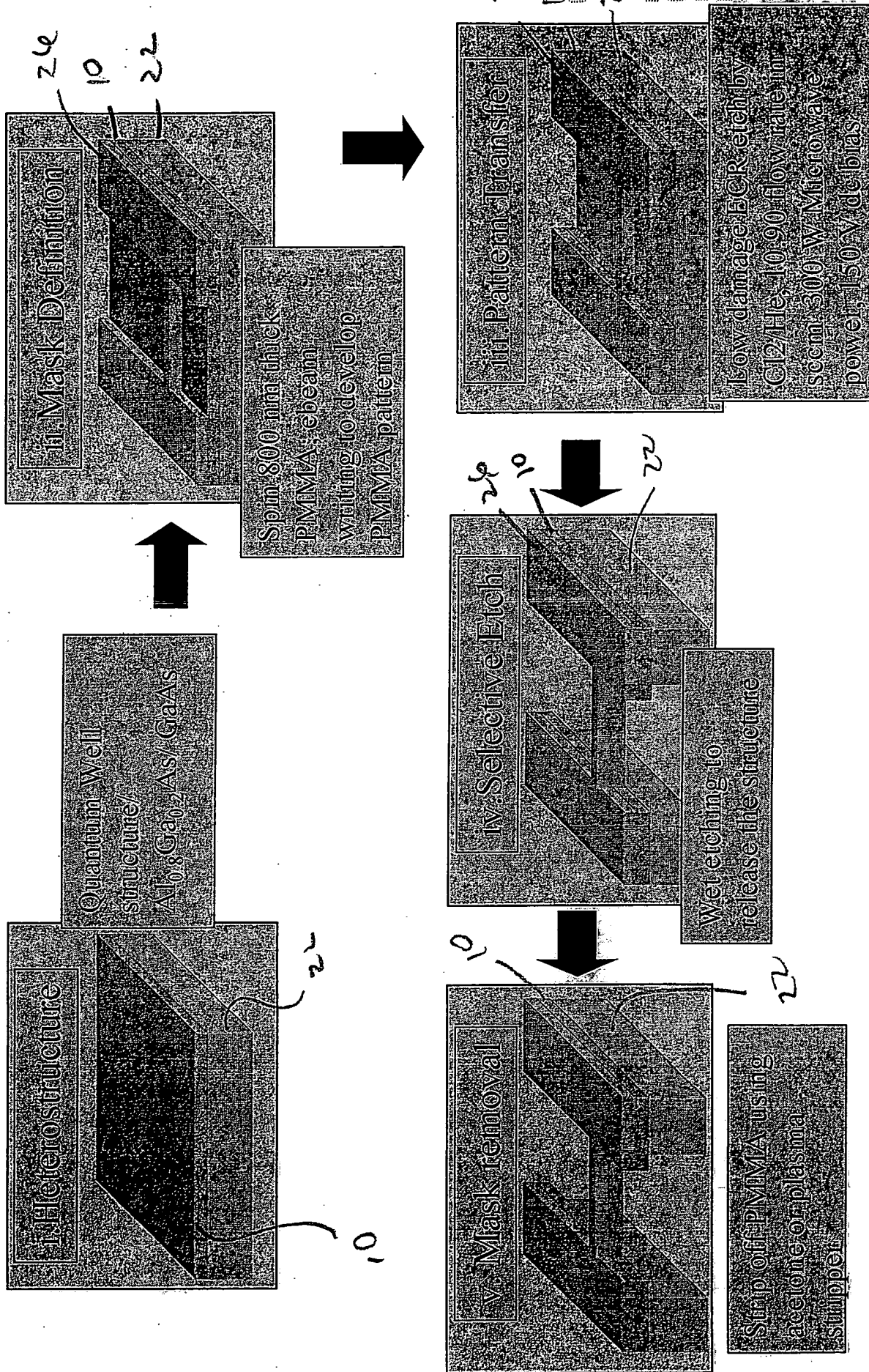


Fig. 3d



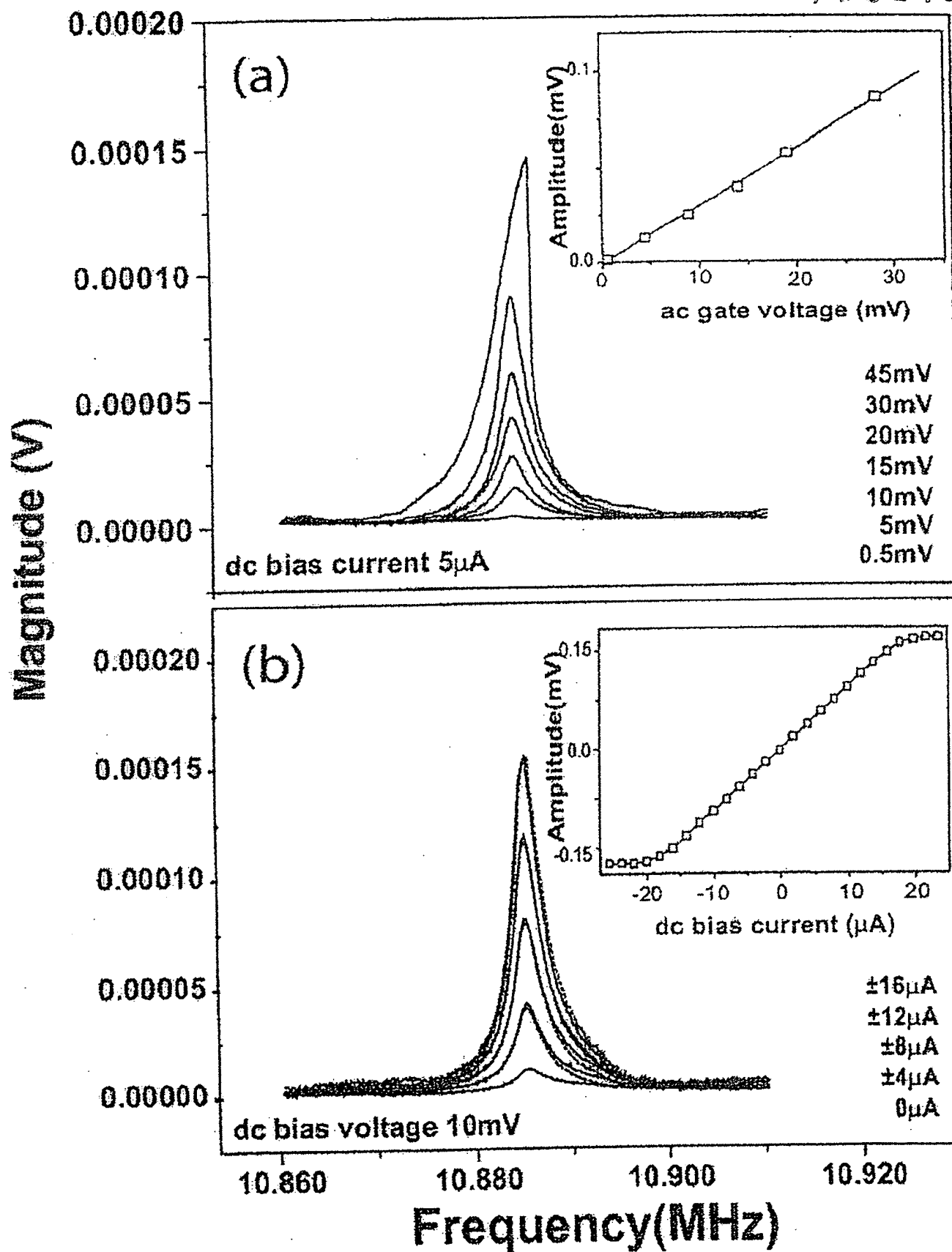


Fig. 4

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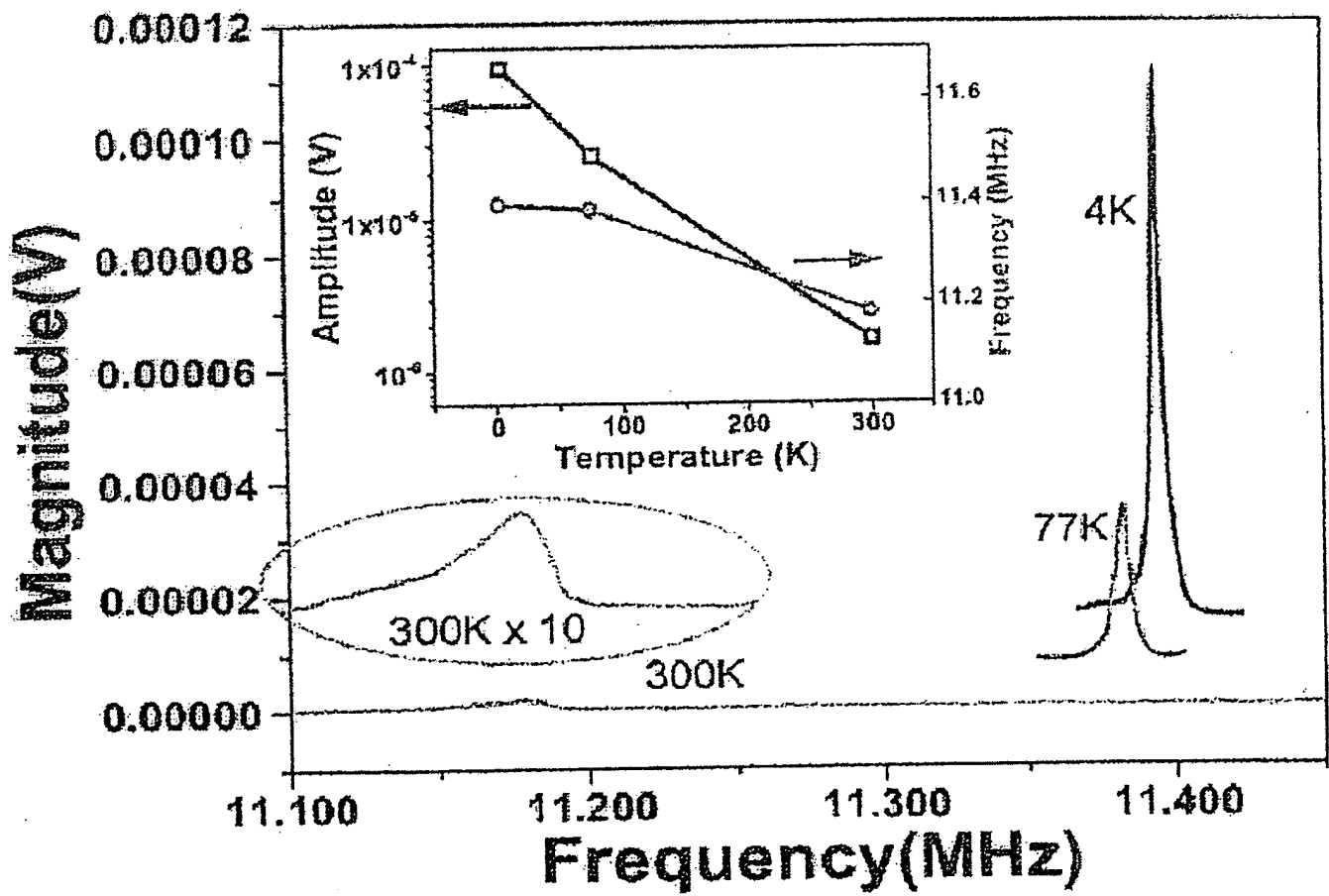


Fig. 5

10/502461

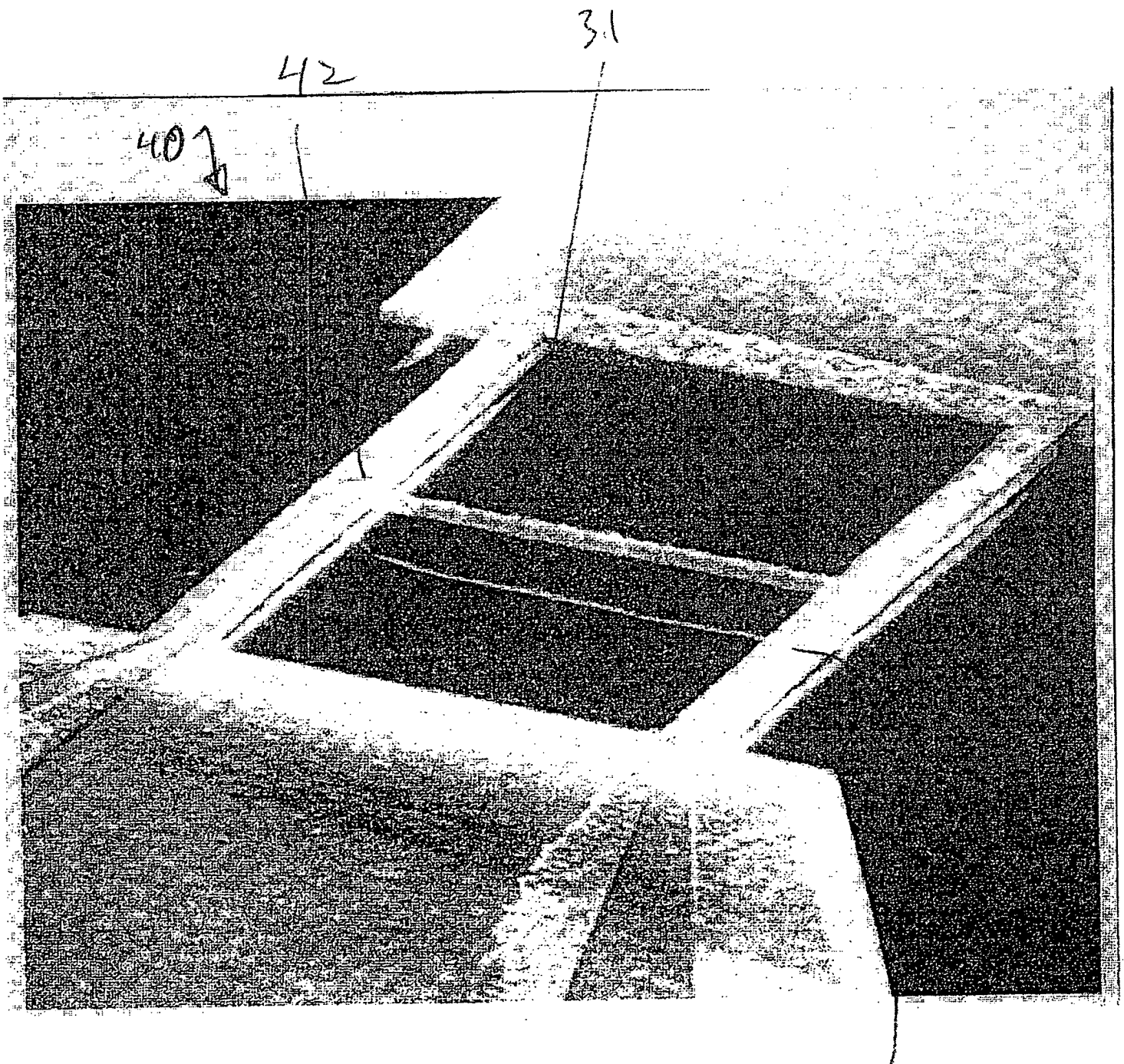


Fig 6

42

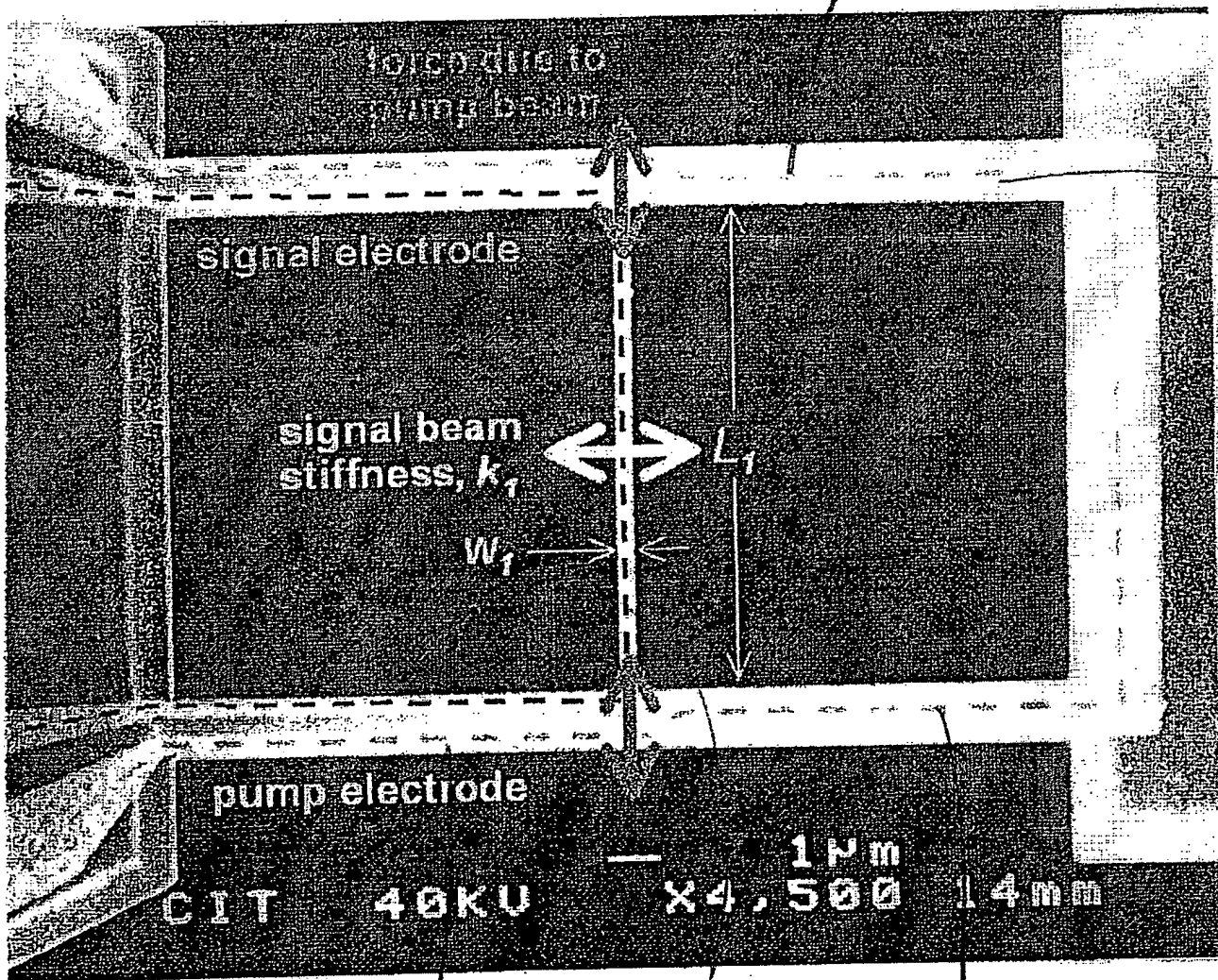


Fig. 7

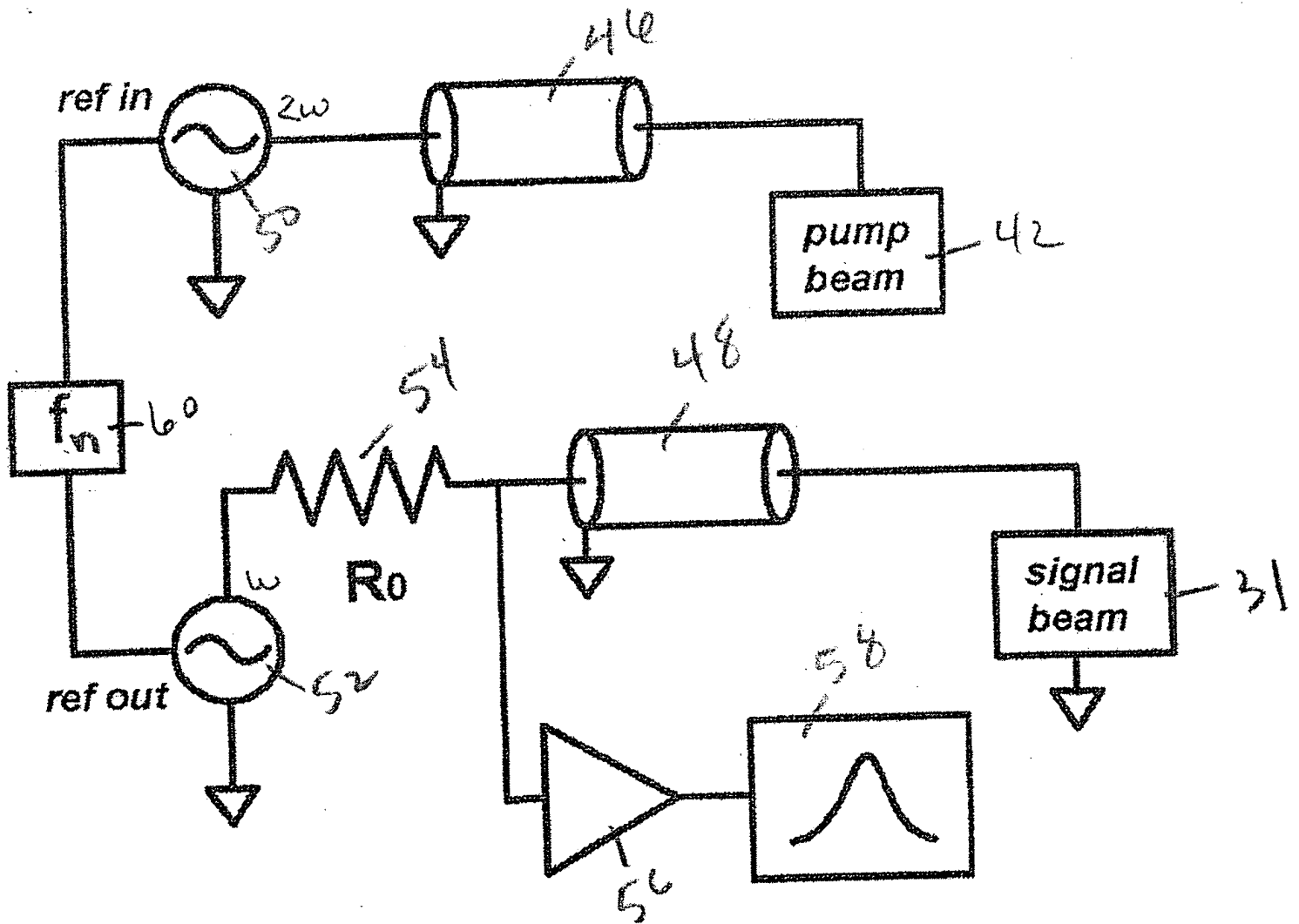


Fig. 8

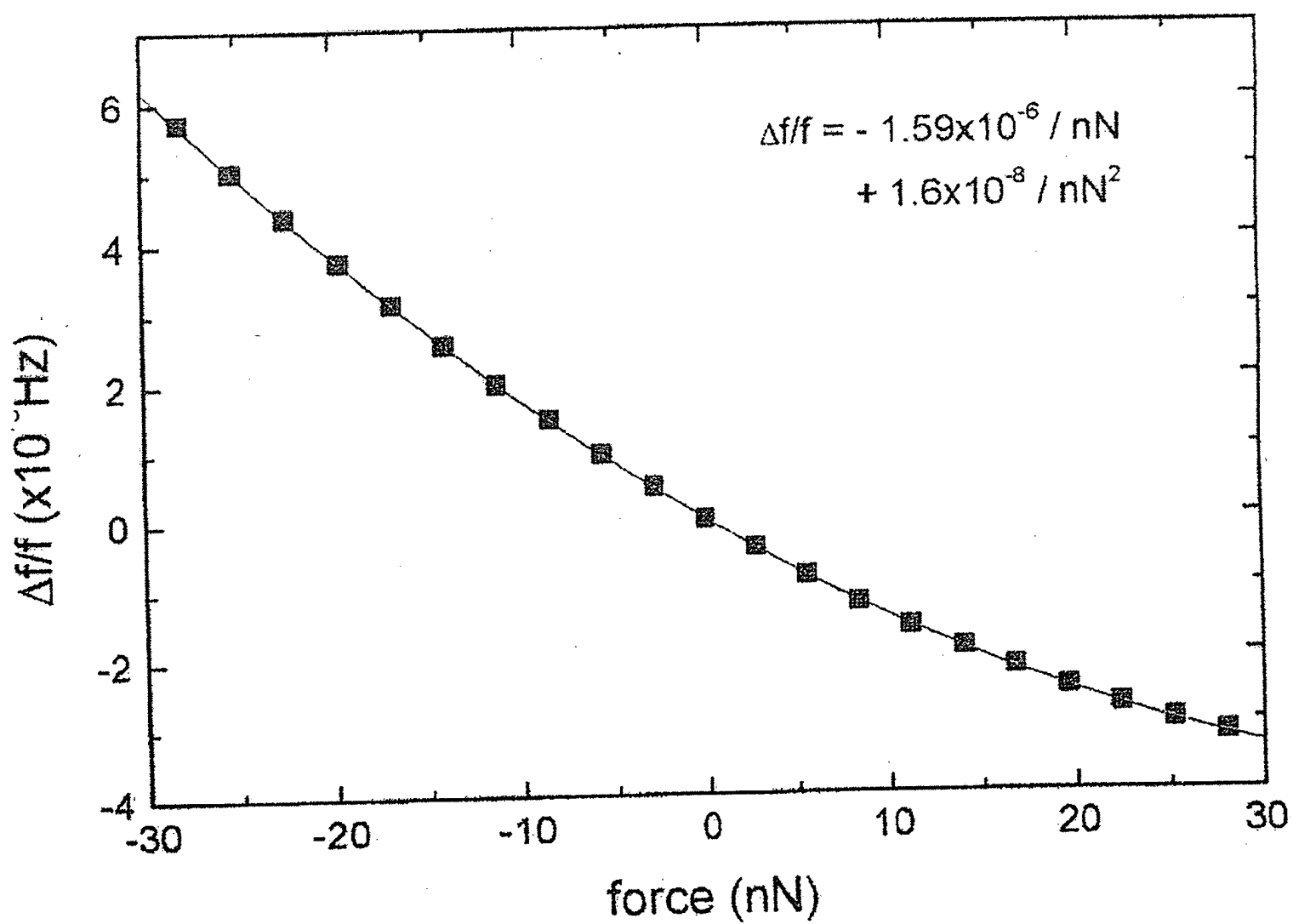


Fig. 9

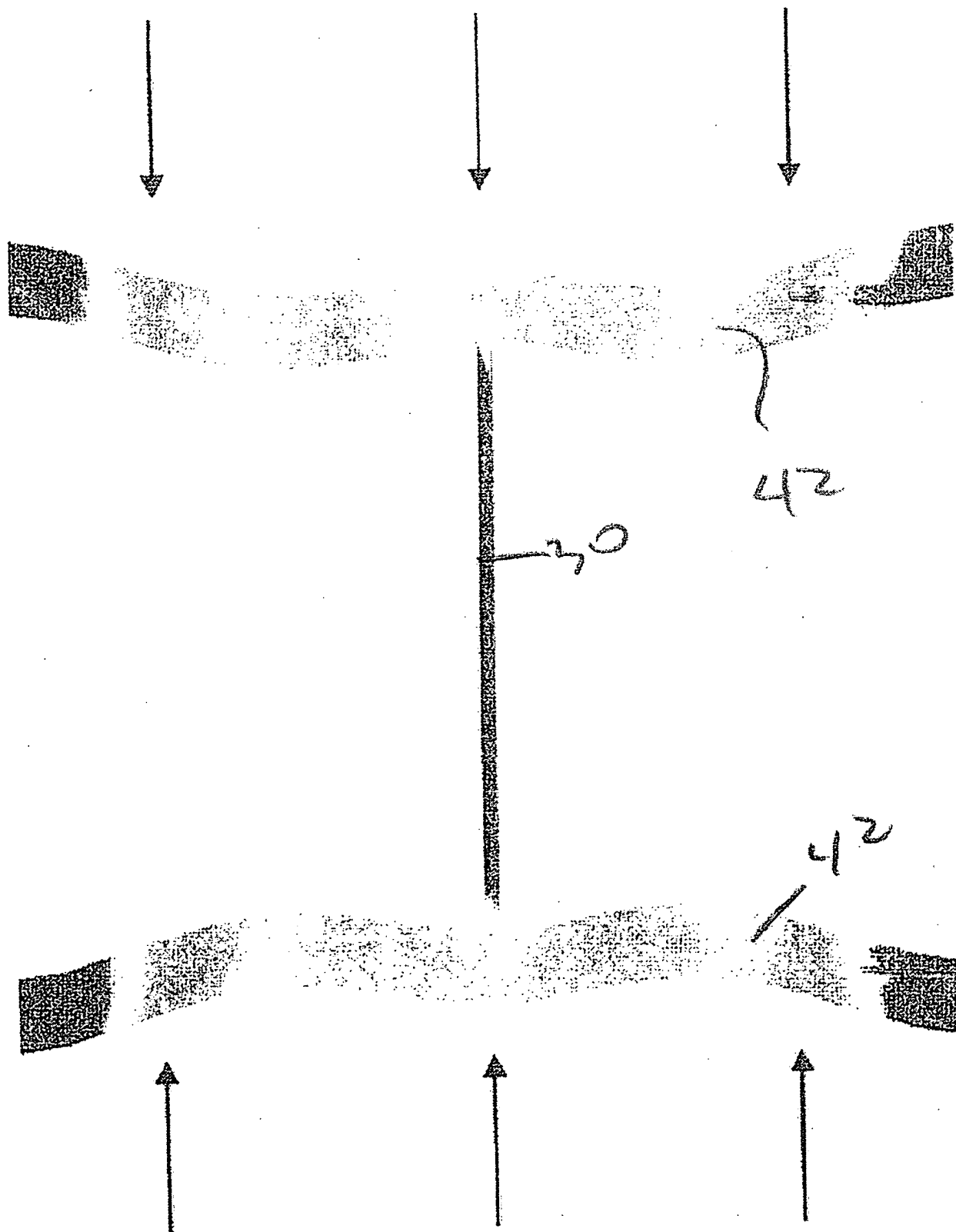


Fig. 10

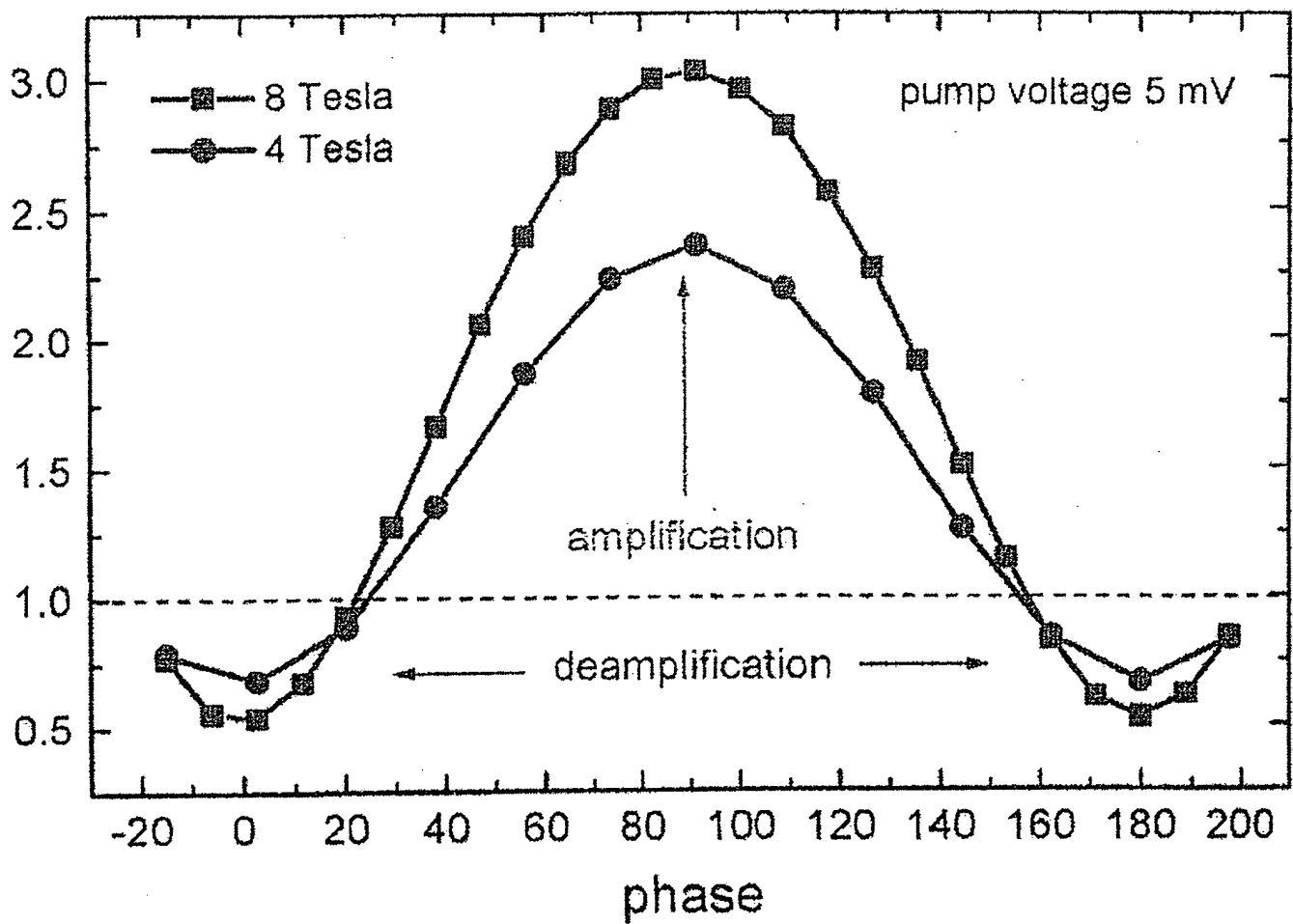


Fig. 11

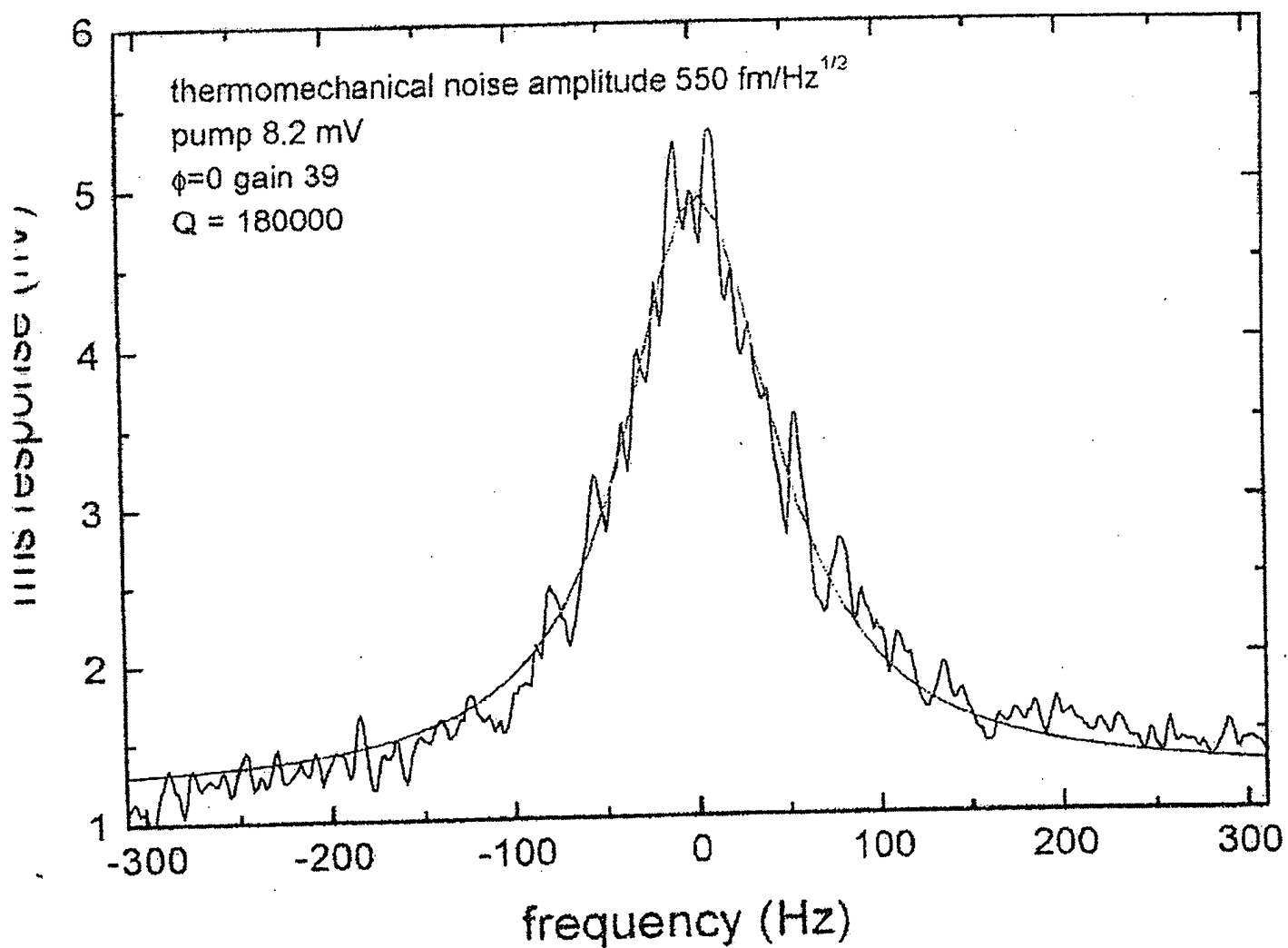


Fig. 13

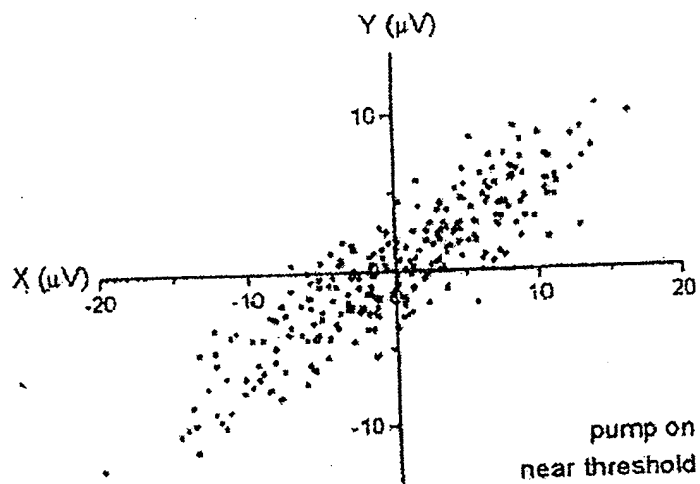
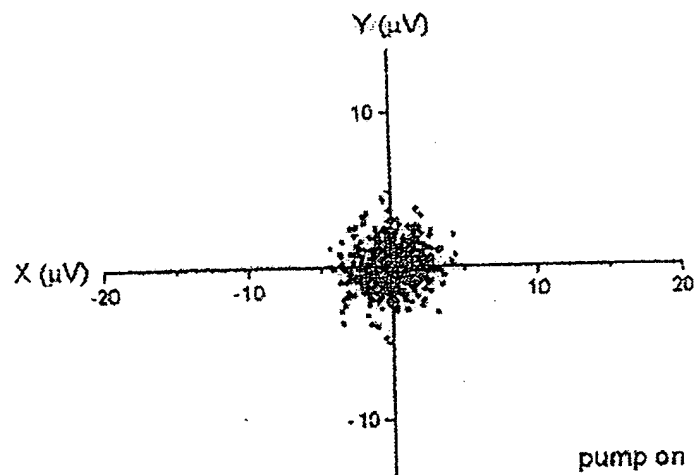
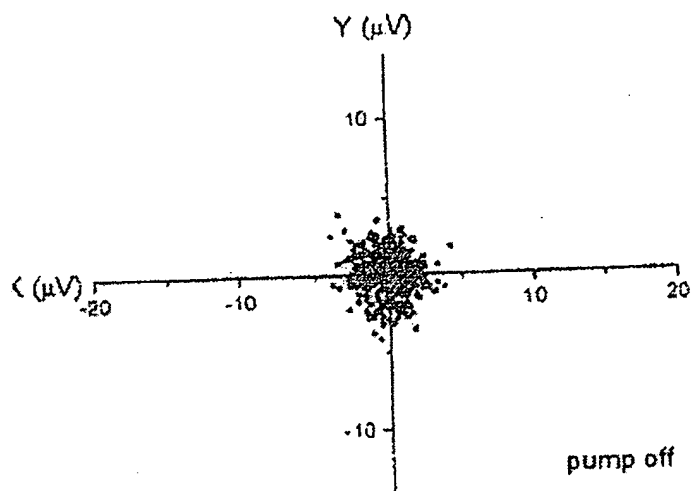


Fig. 14

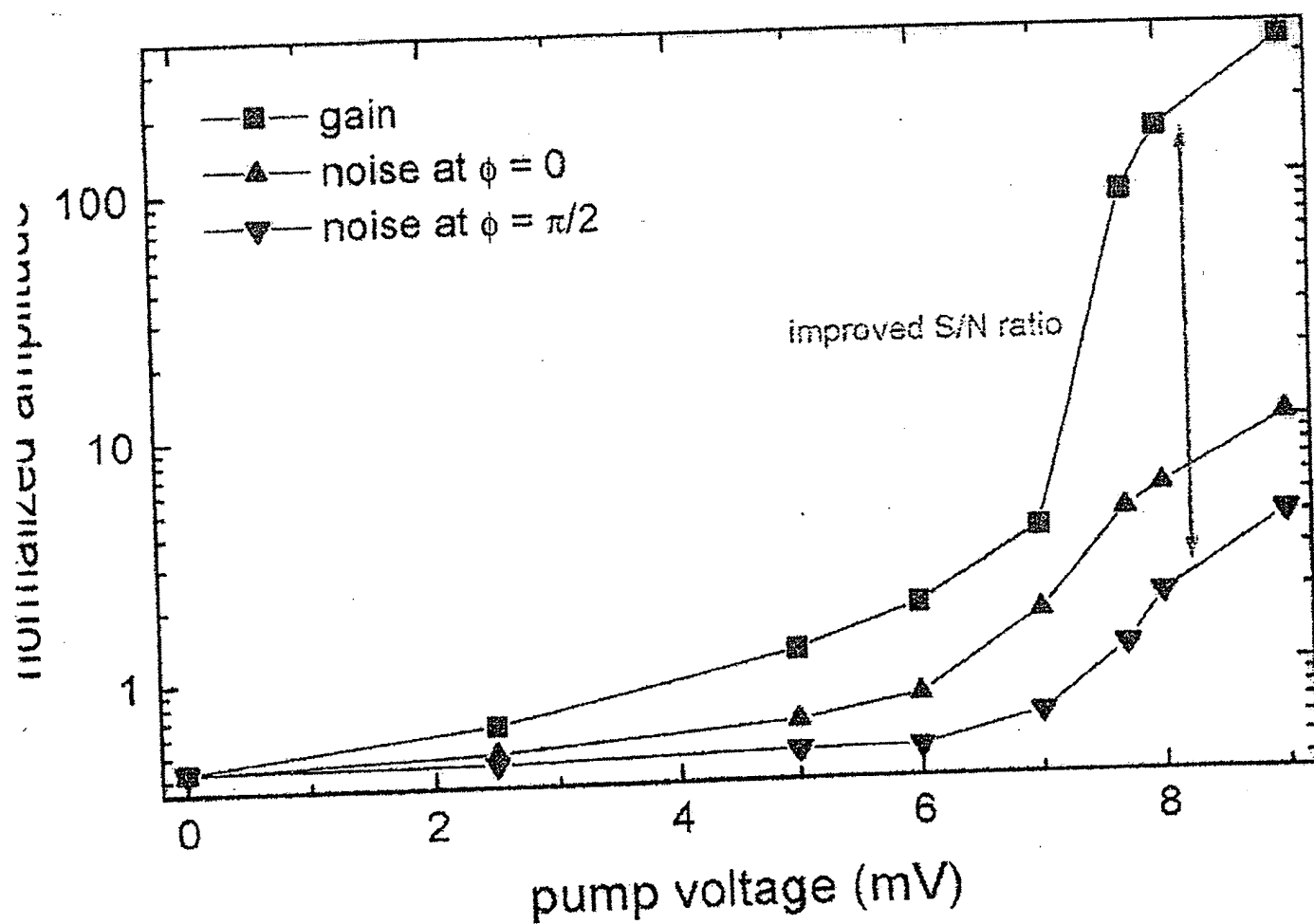


Fig. 15

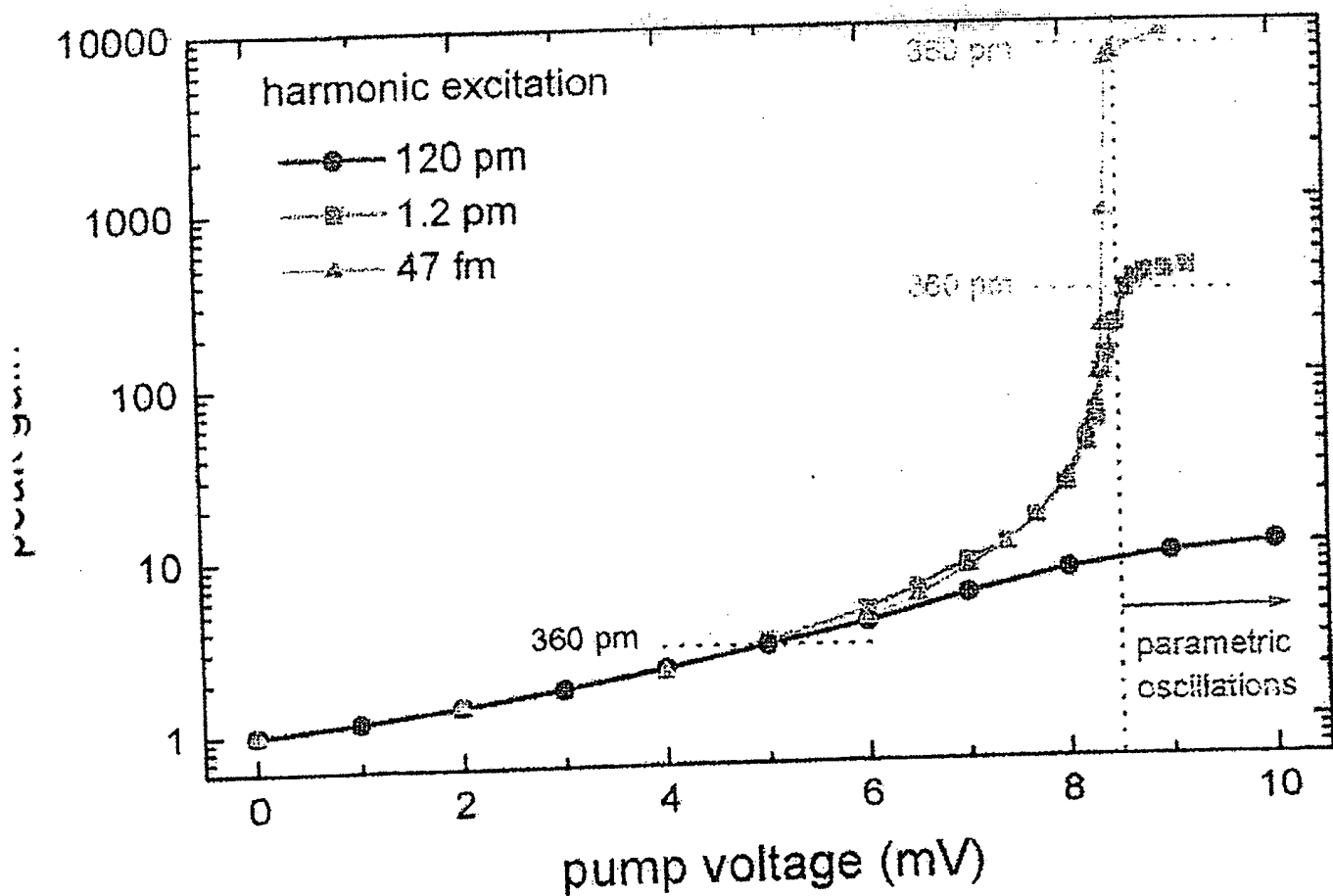
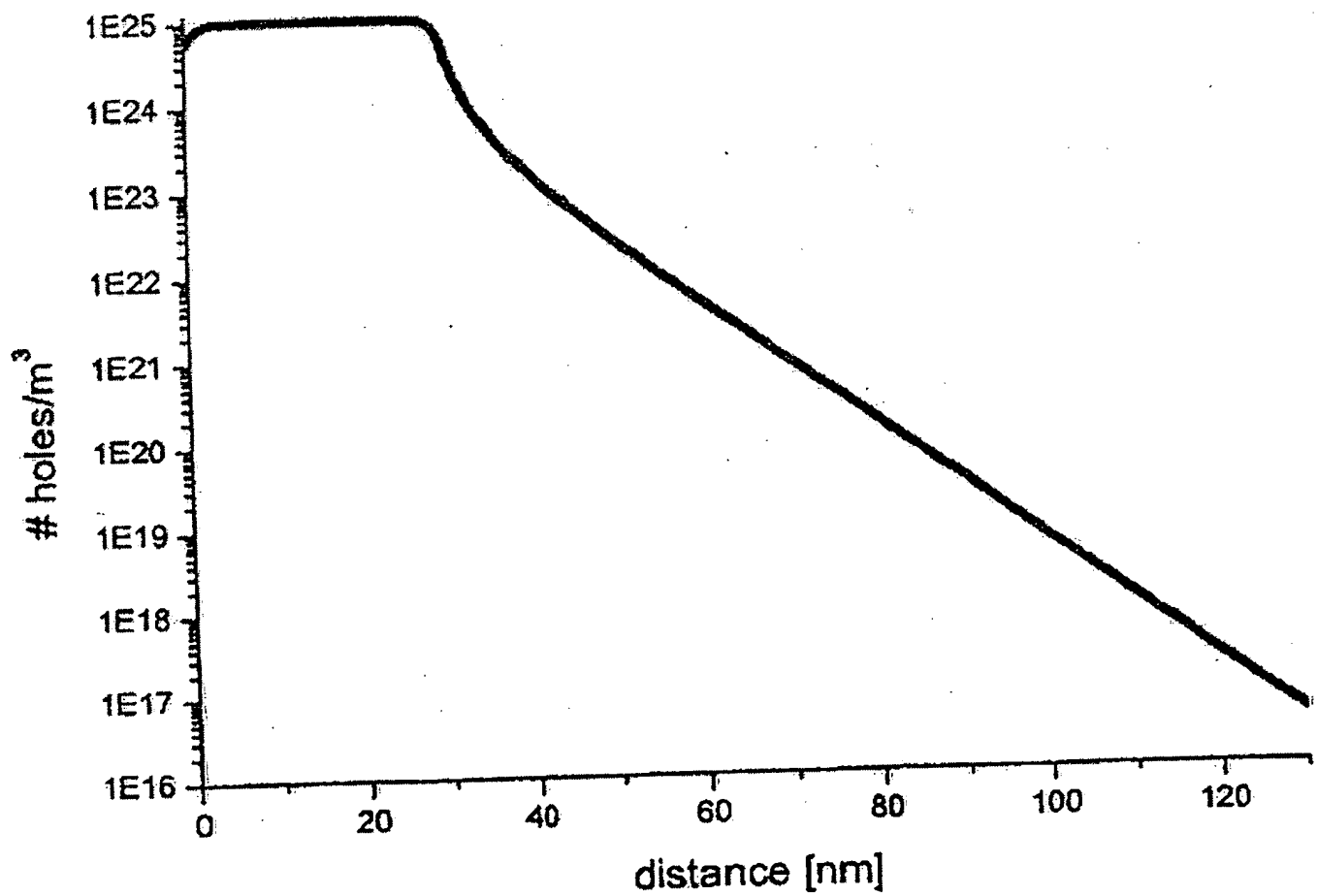


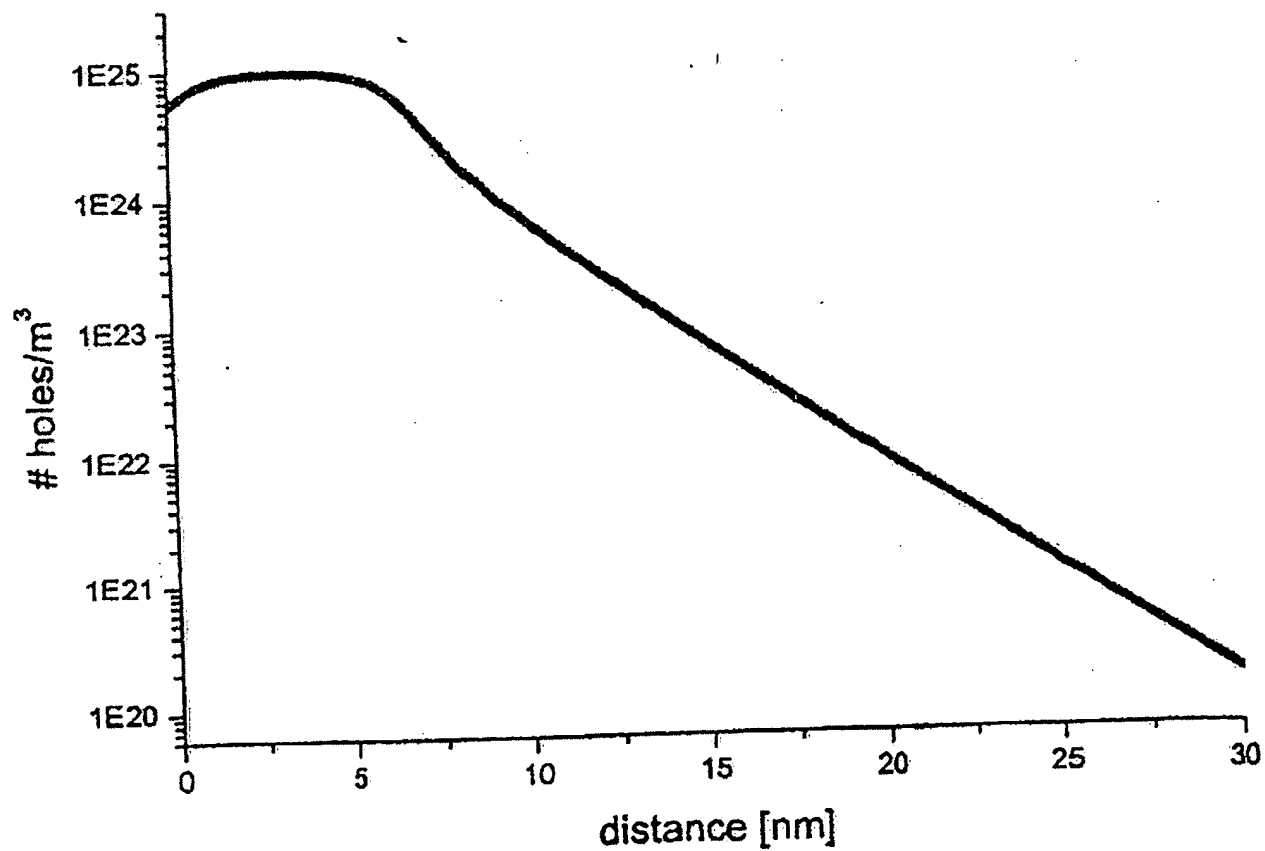
Fig. 16

Fig. 17



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Fig. 18



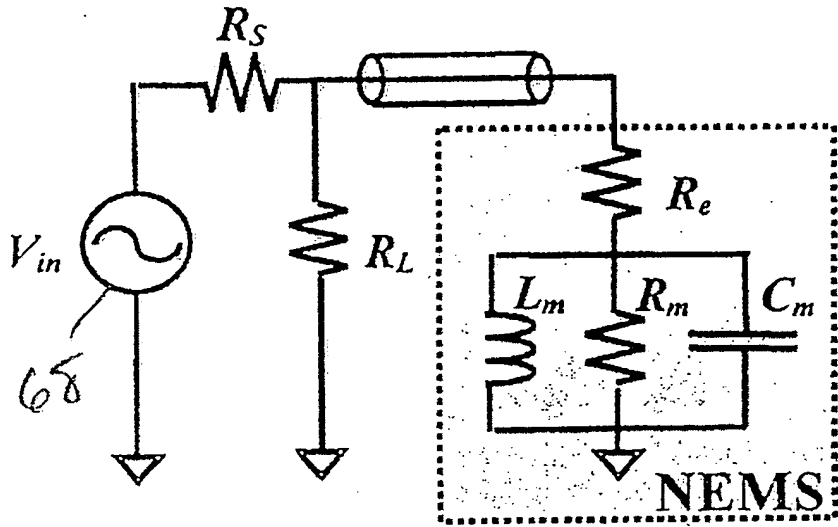


Fig. 19(a)

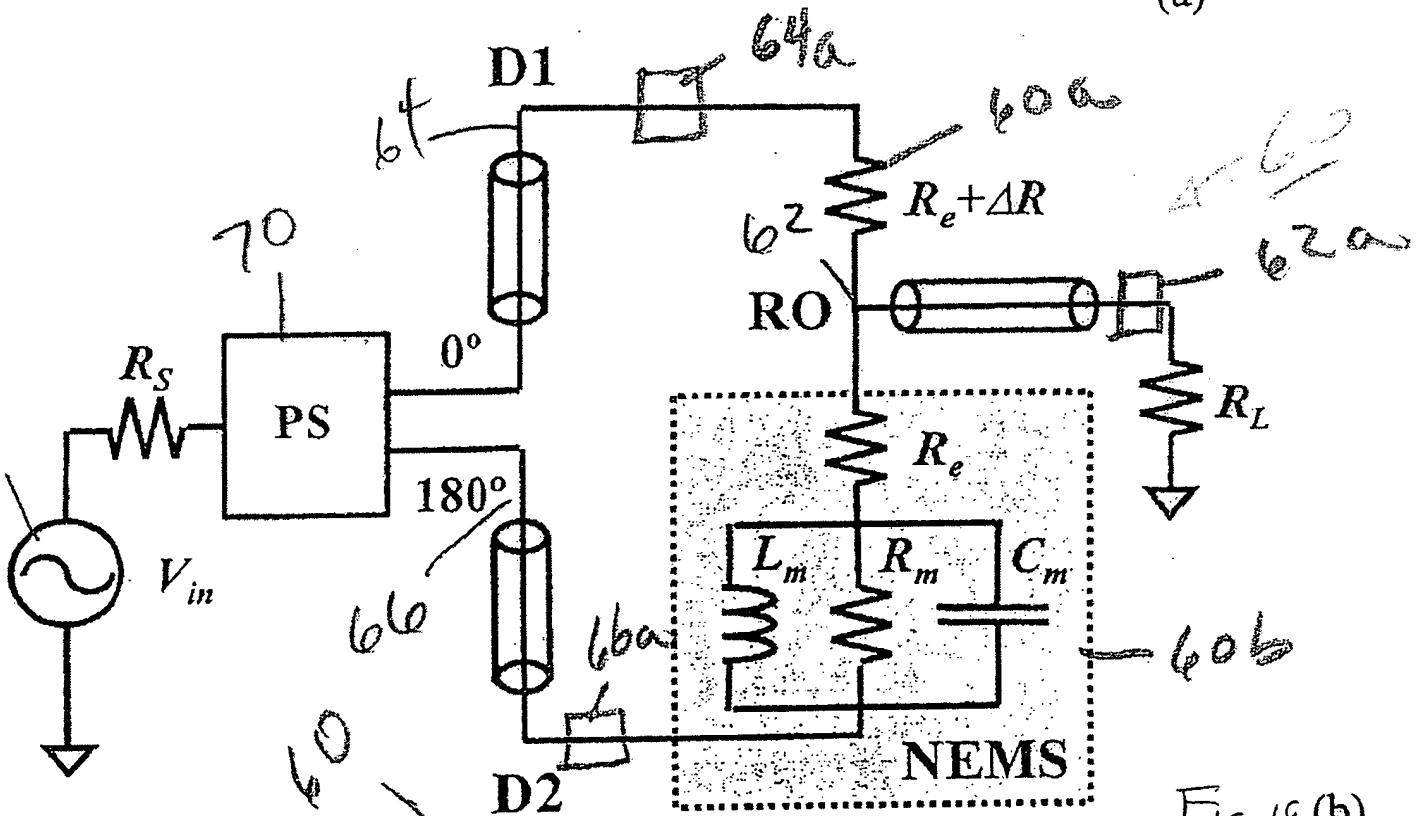


Fig. 19(b)

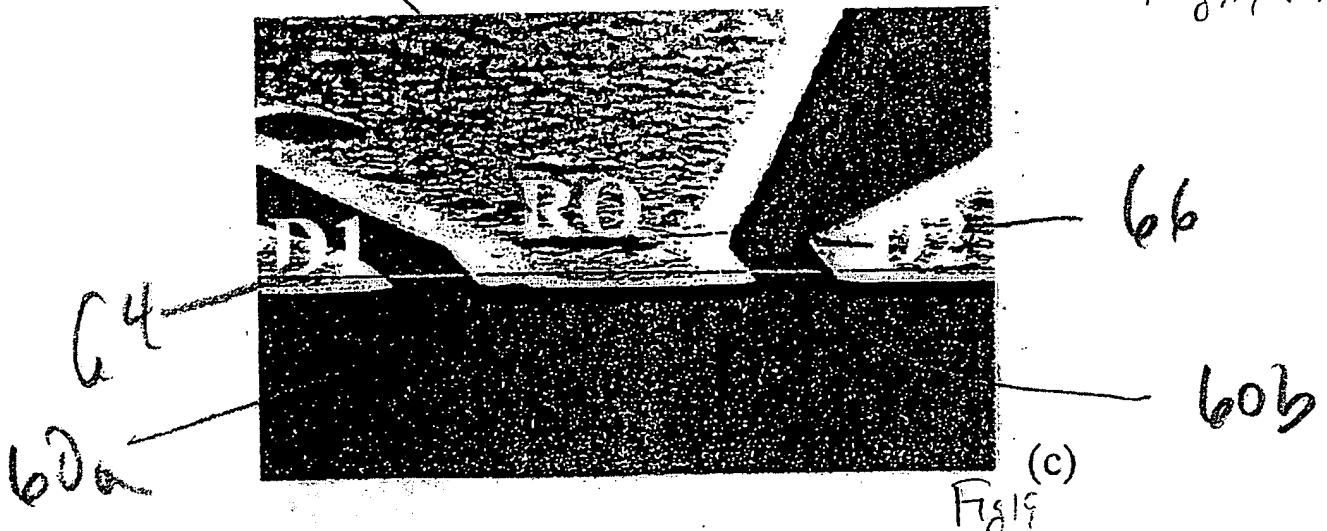
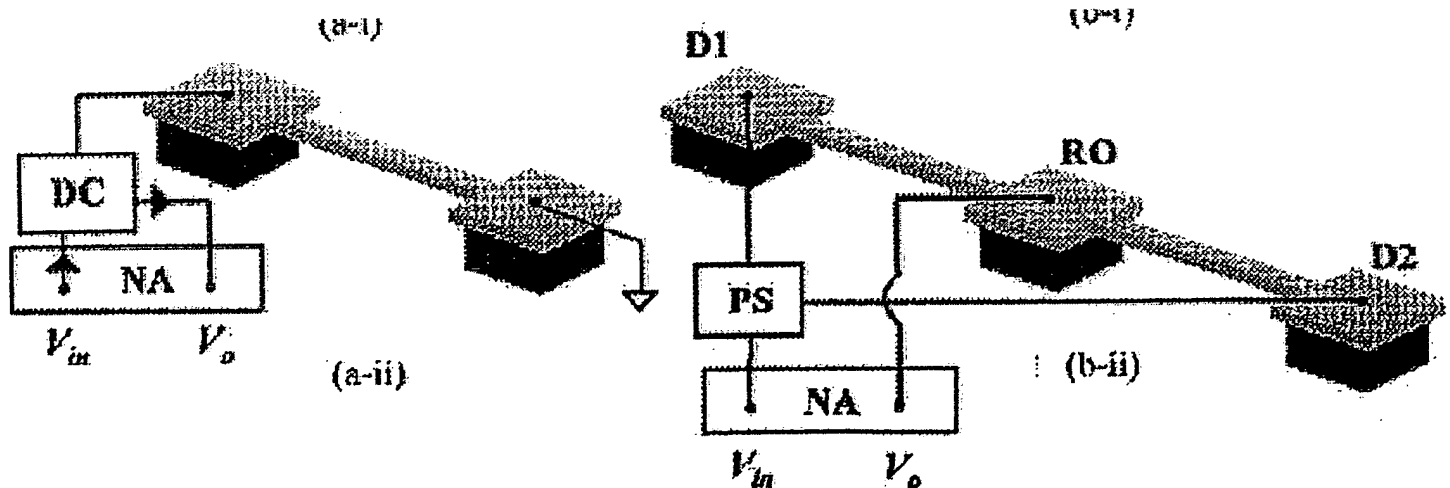


Fig. 19(c)

Fig 19d



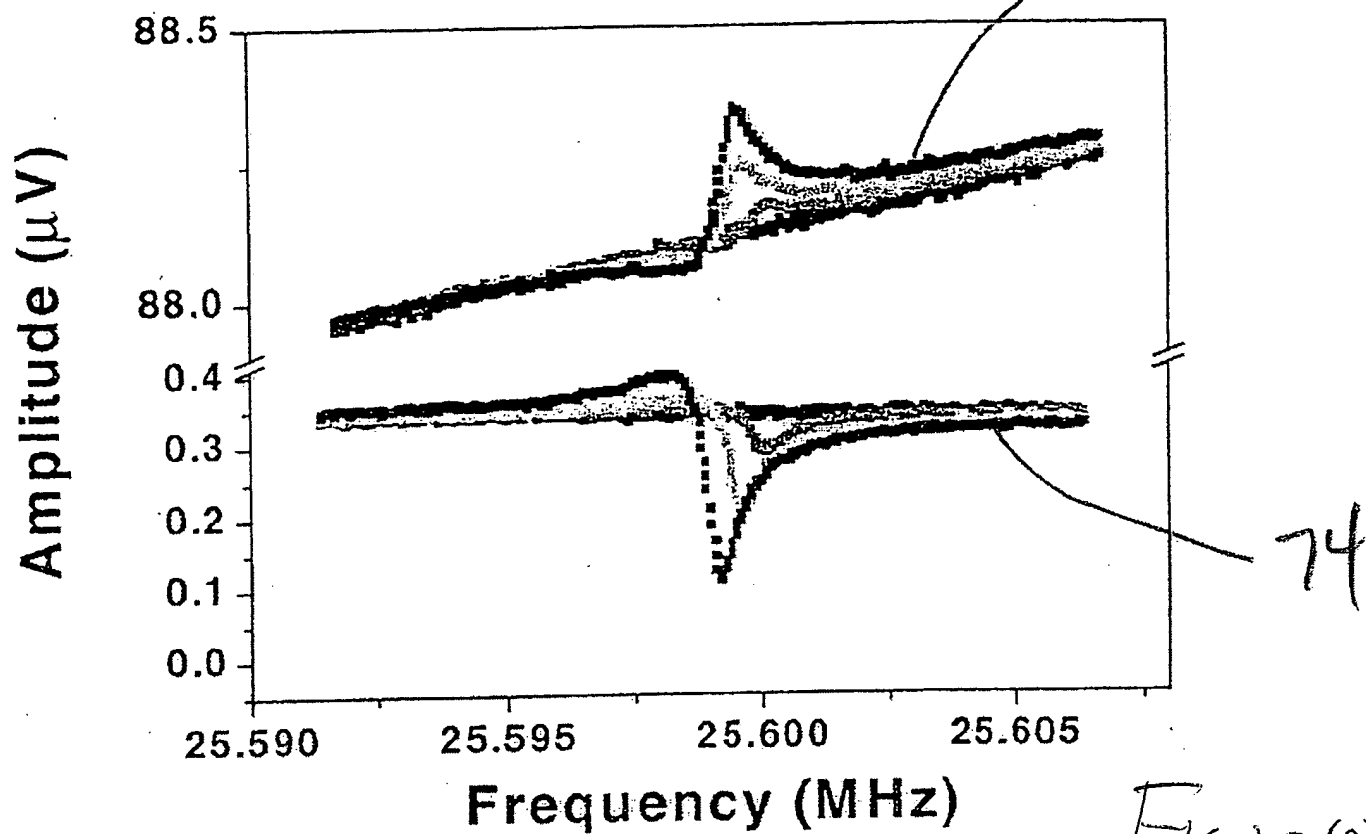


Fig 20 (a)

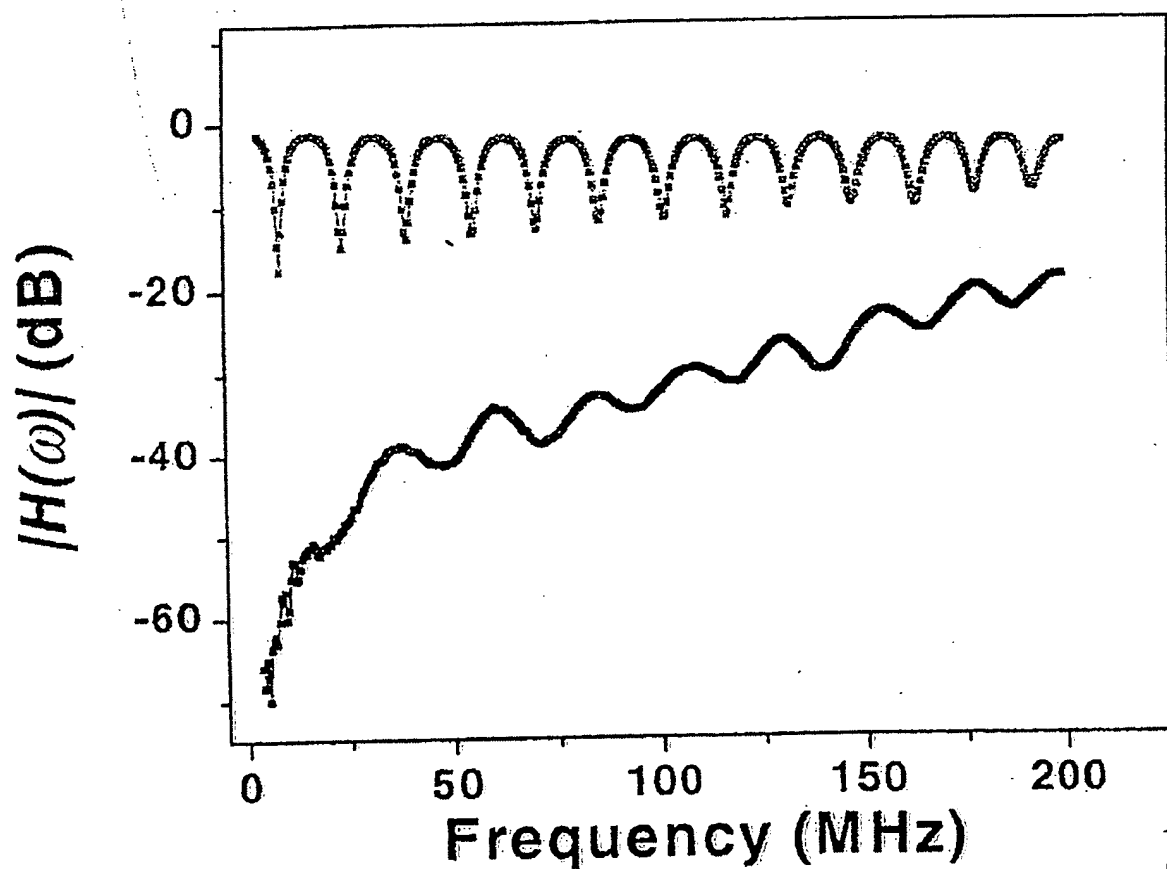


Fig 20 (b)

10/502461

Fig. 21

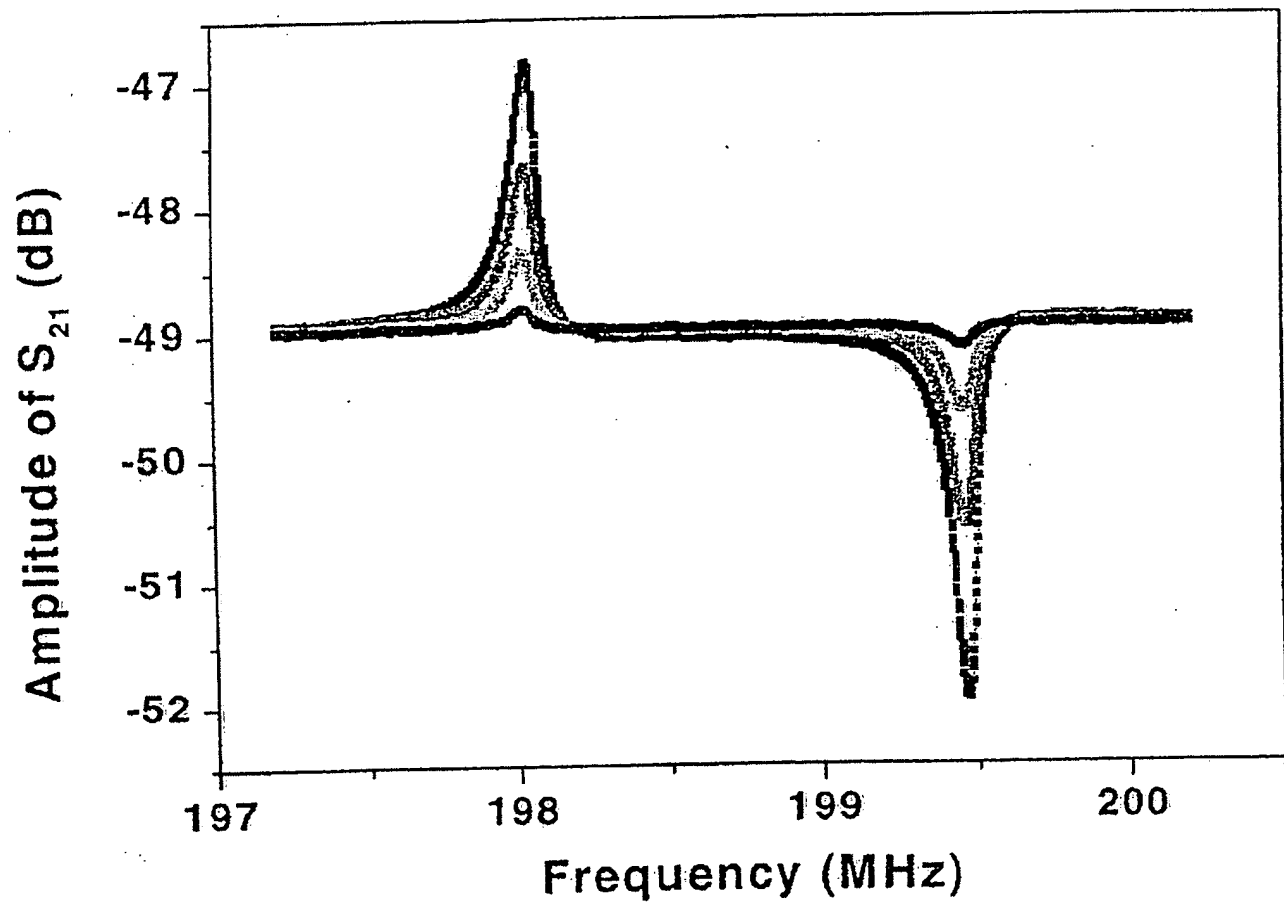


Fig. 22

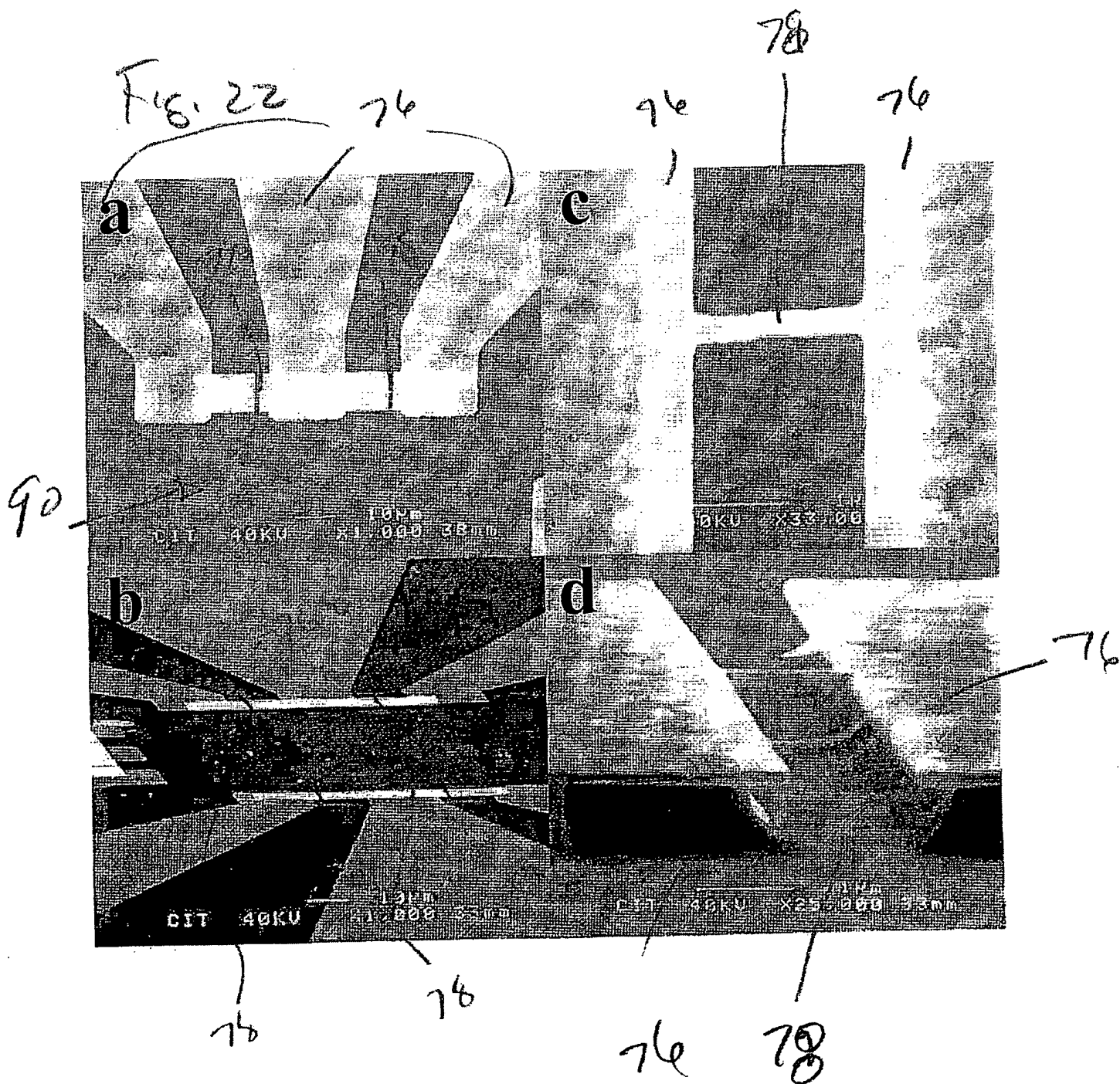


Fig. 23

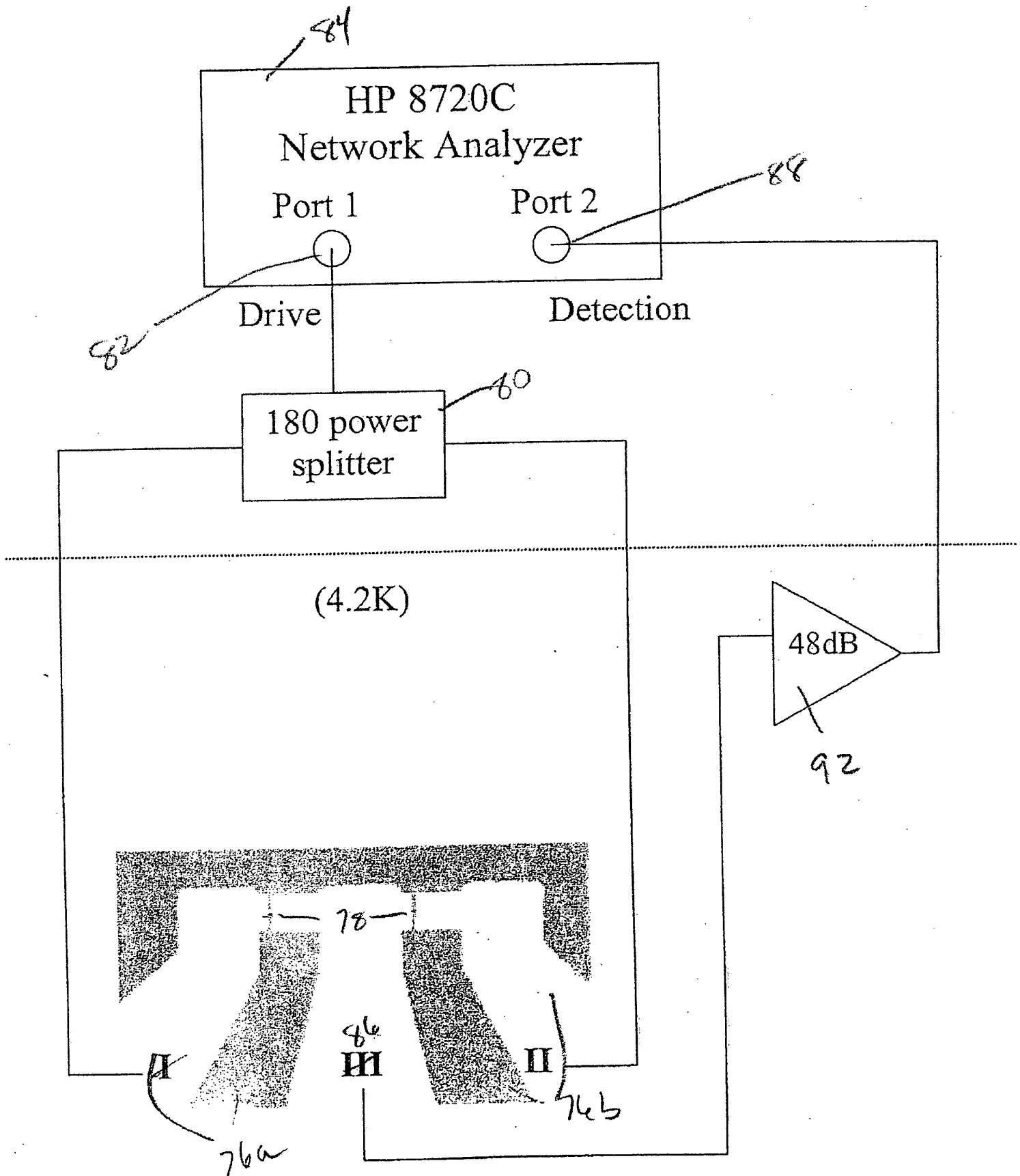


Fig. 24

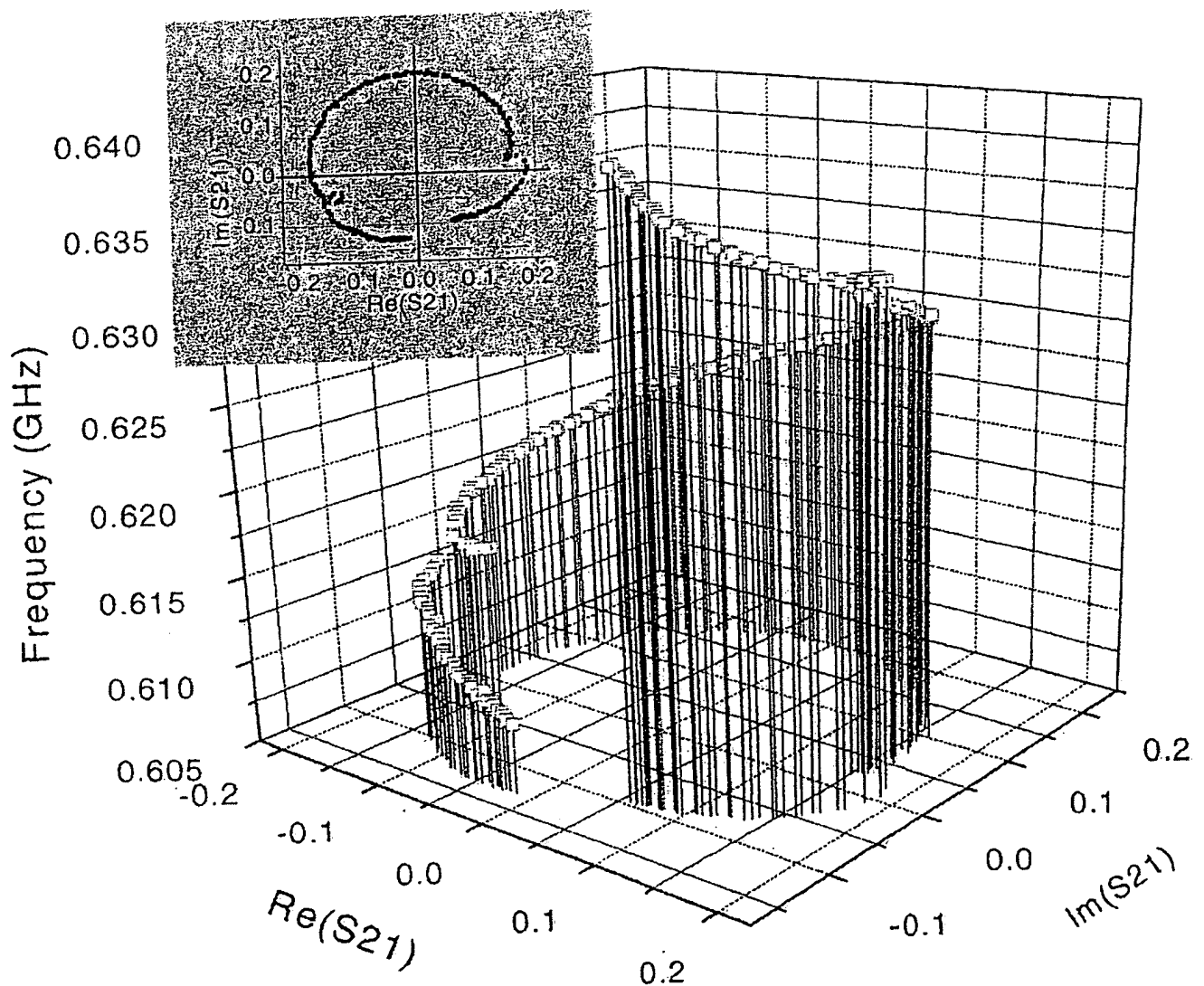


Fig. 25

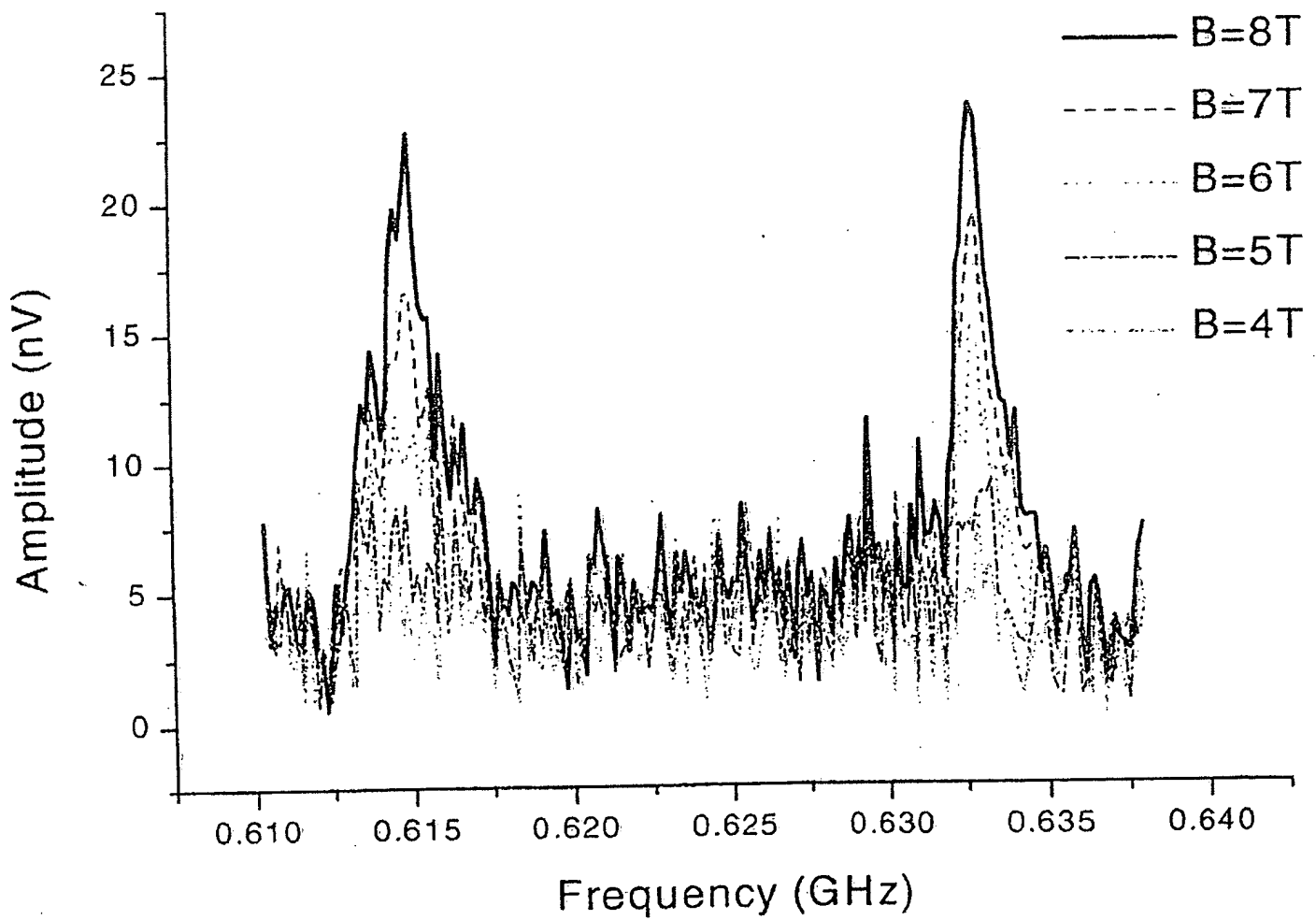
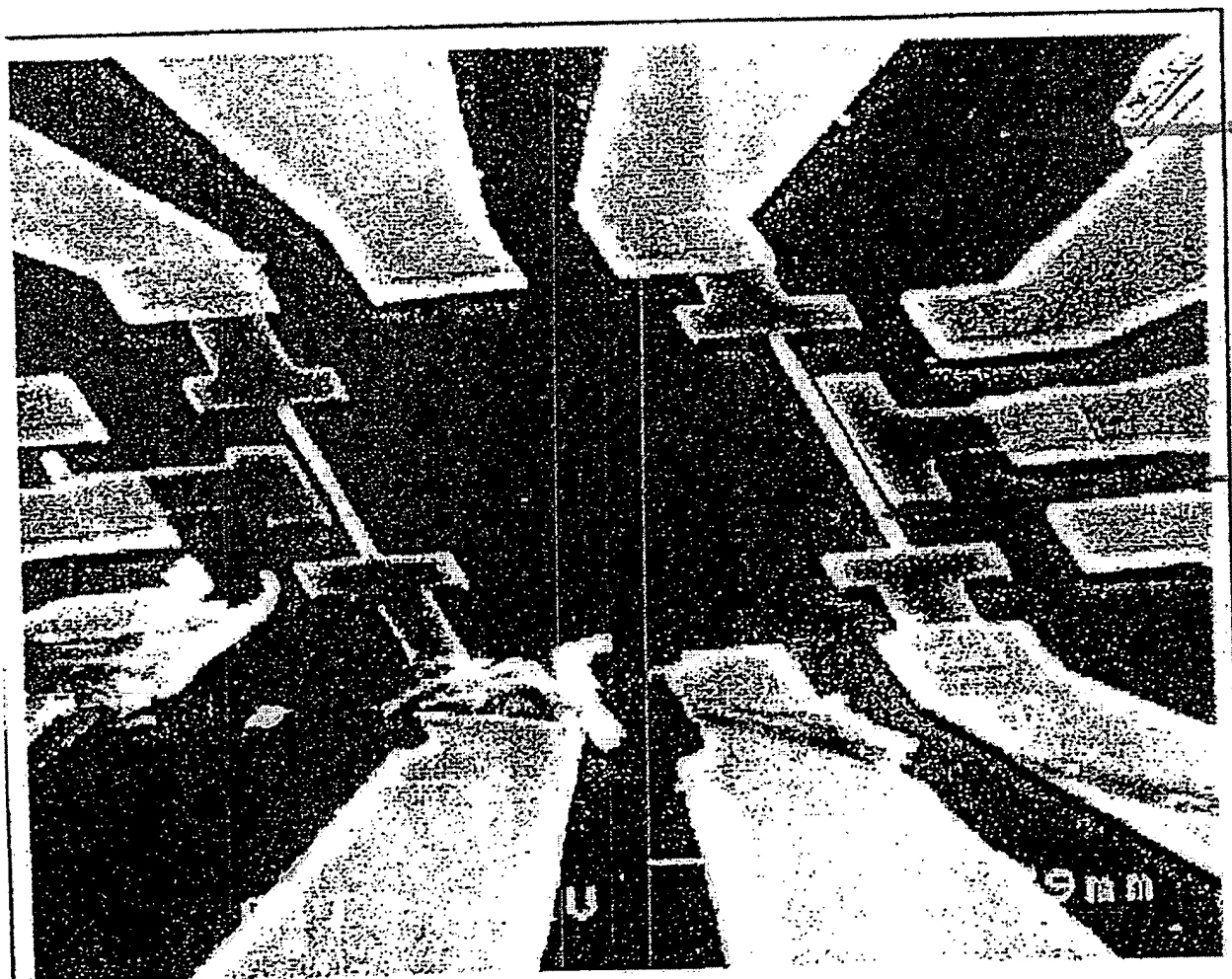


Fig. 26



95

94

Figure 1. Device photo

2le

Fig. 27

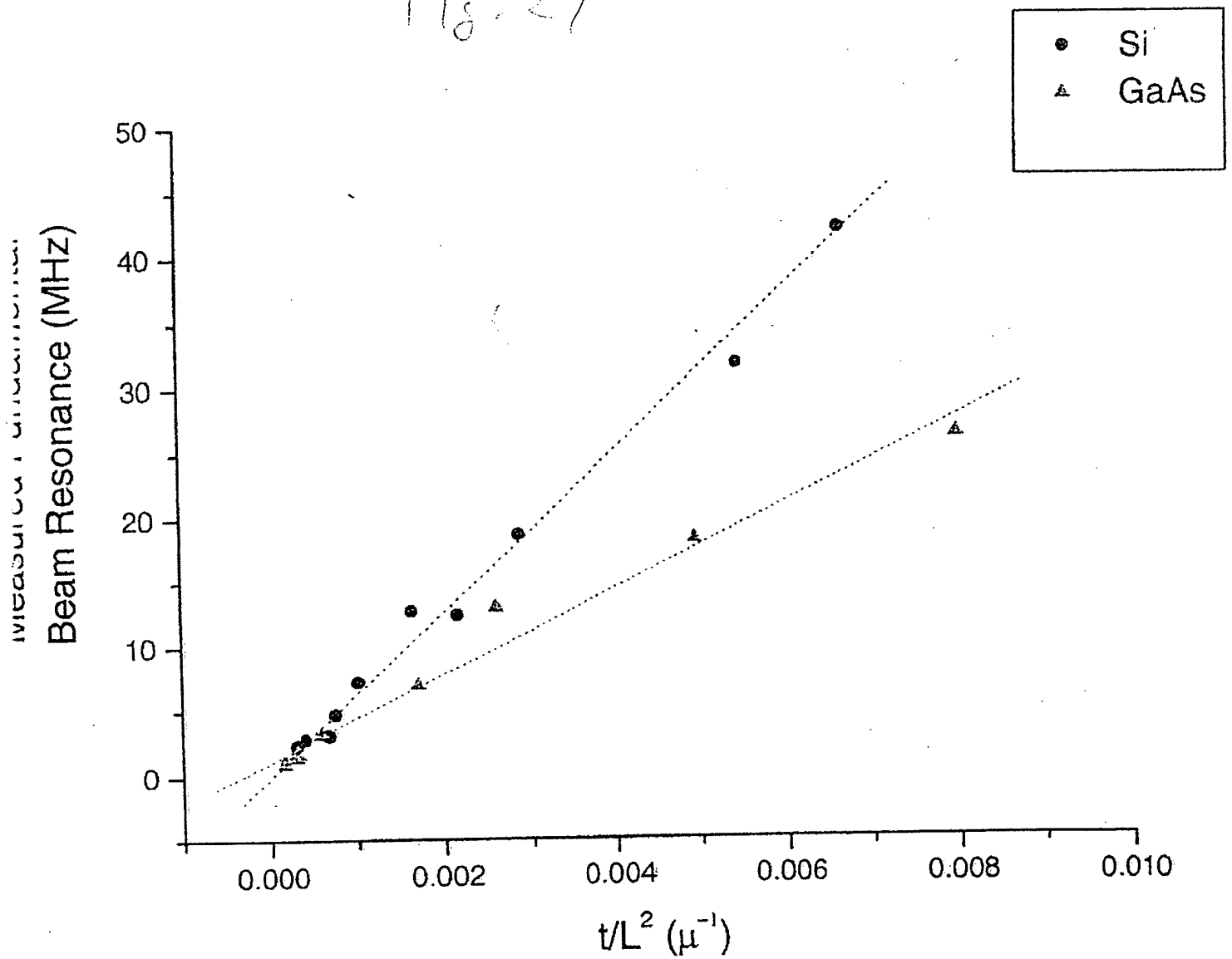
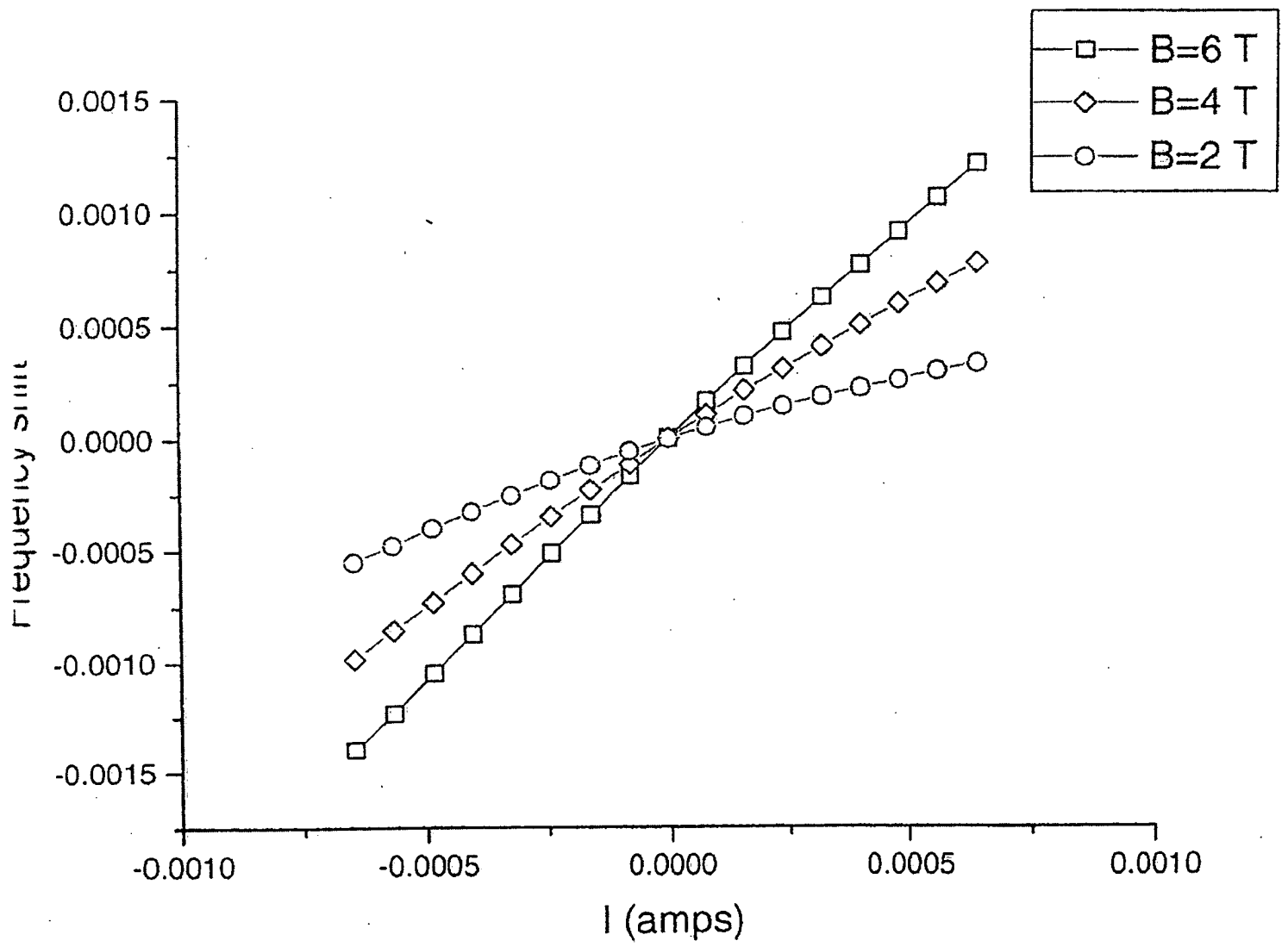
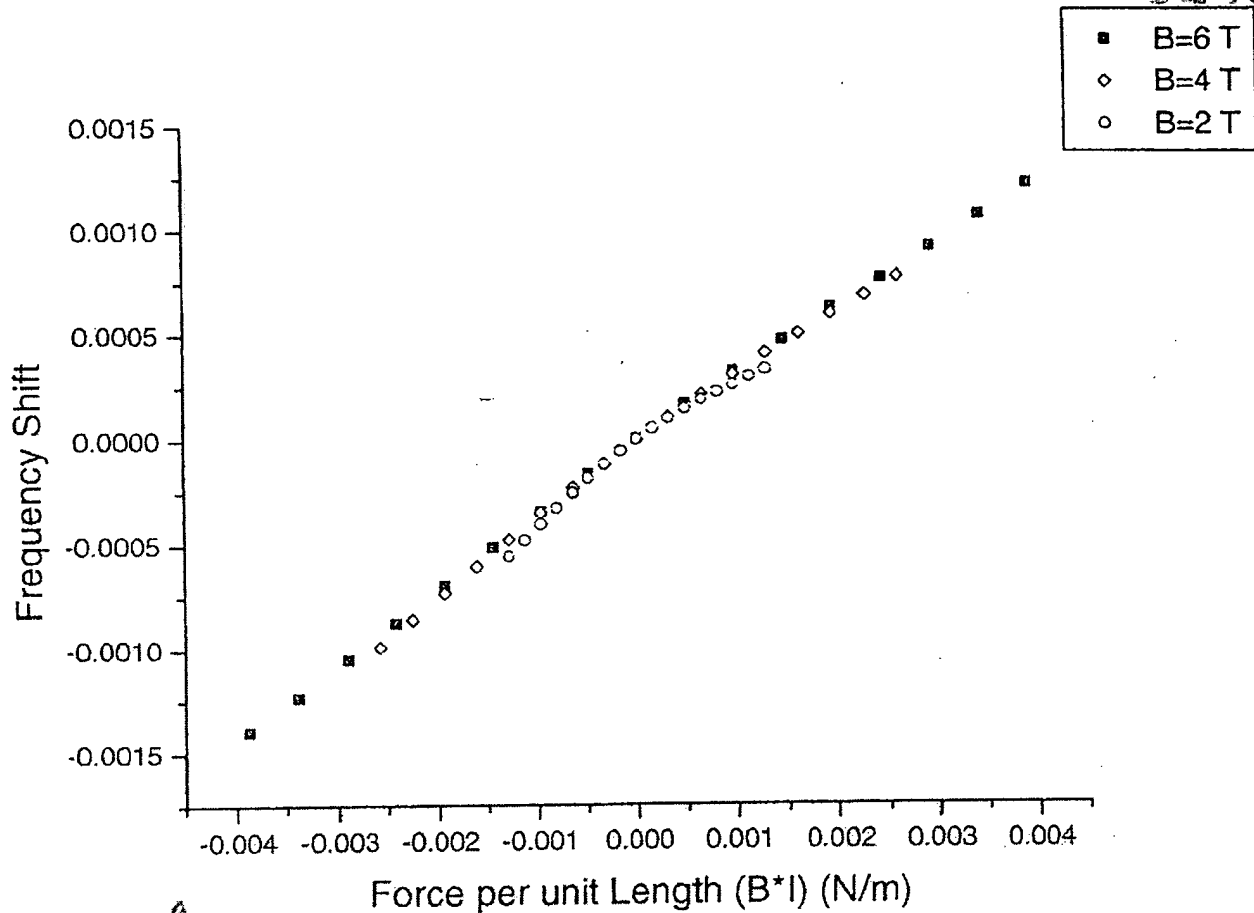


Fig. 28





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Figure 3. Frequency Shift as in Figure 3 plotted as a function of applied force.

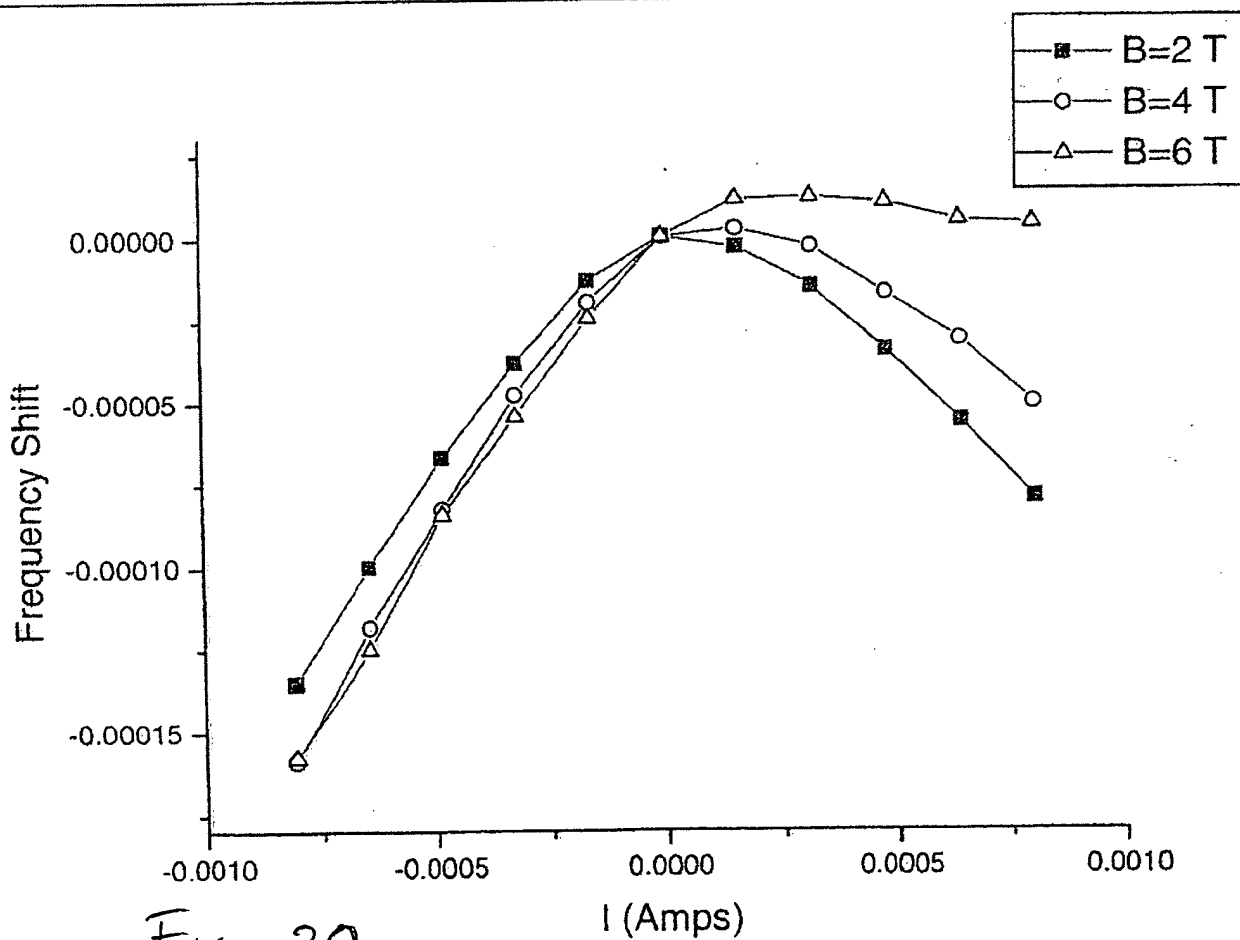


Fig. 30

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Fig. 31

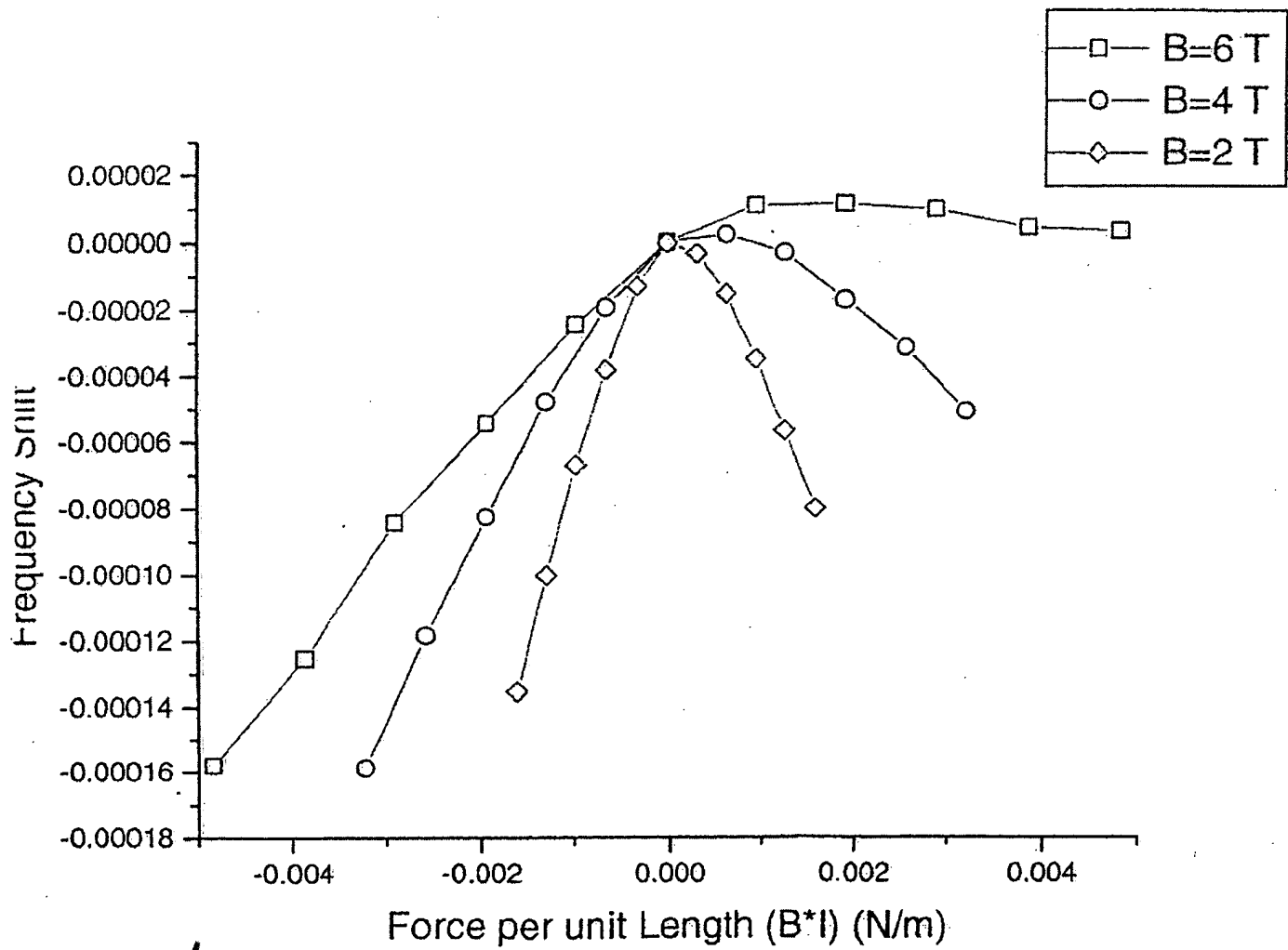


Fig. 32

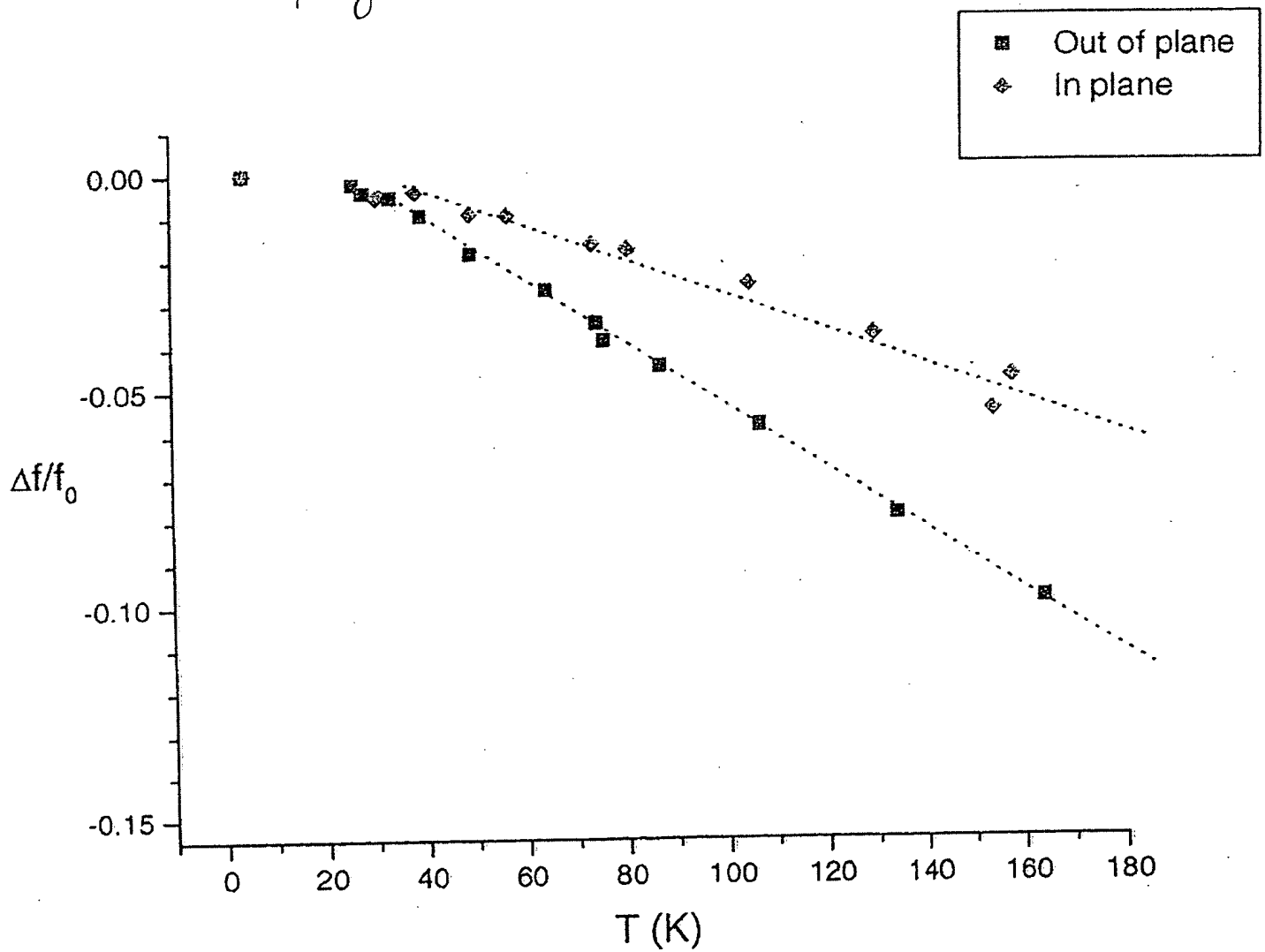
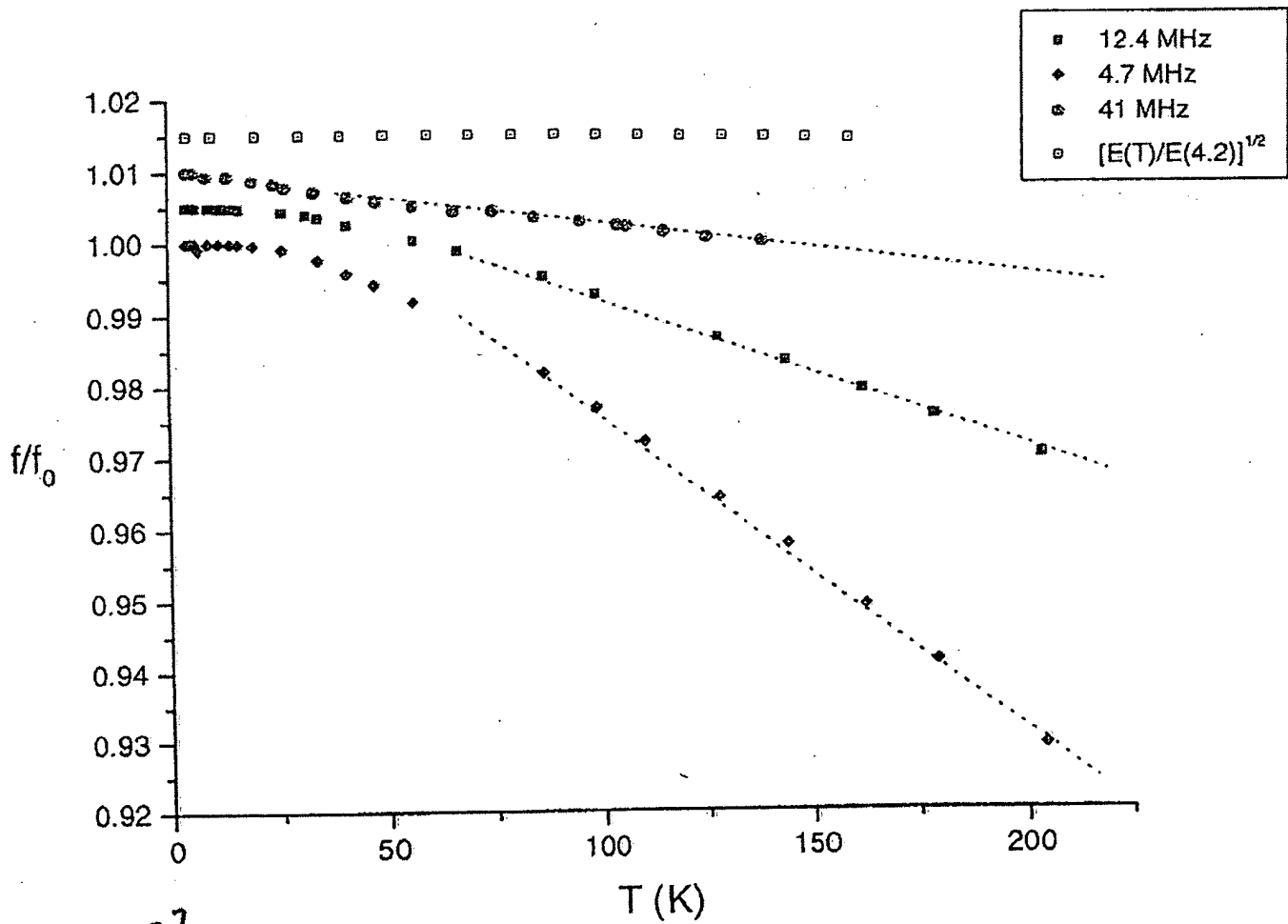


Fig. 33



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Fig. 34

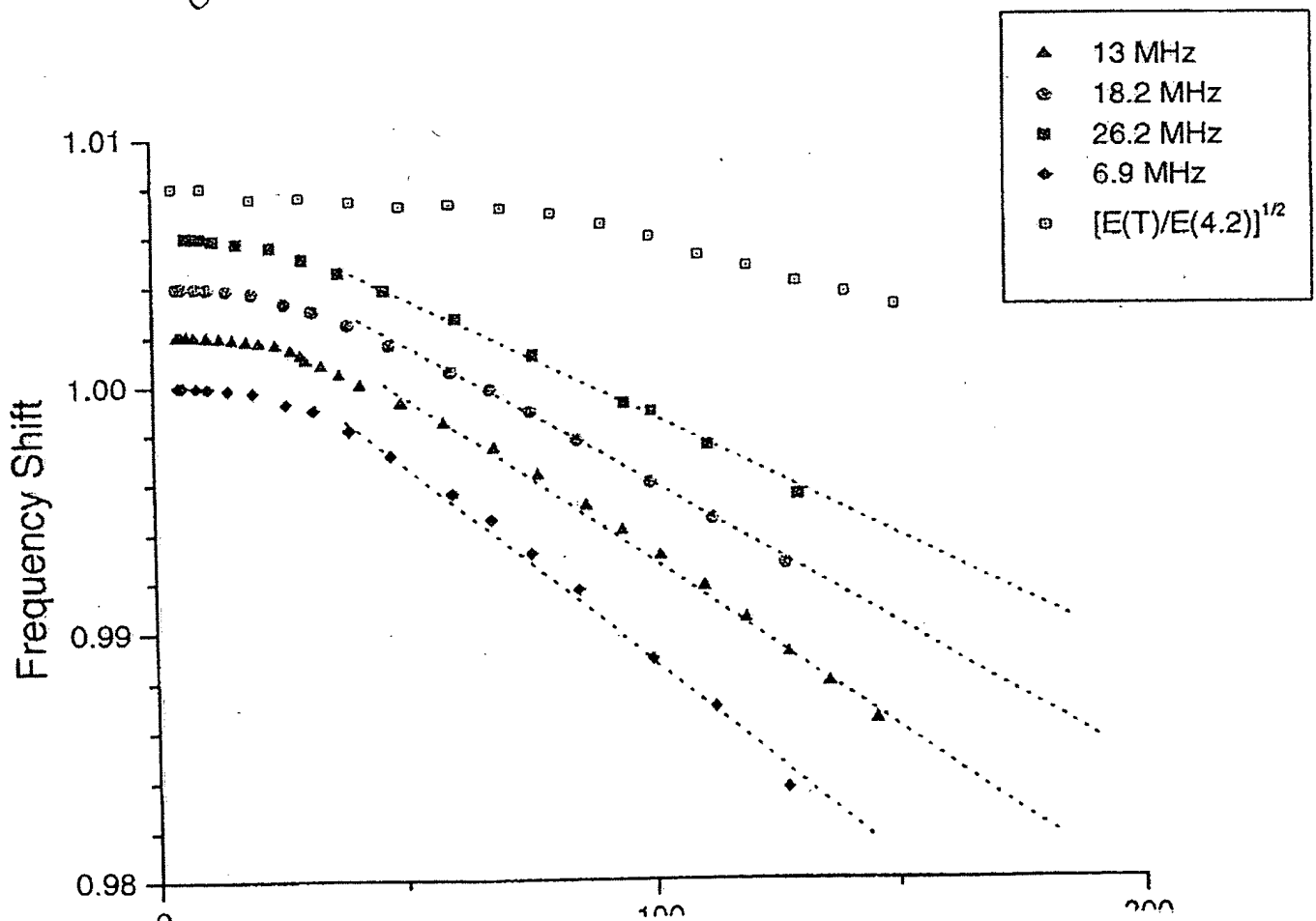


Fig. 35

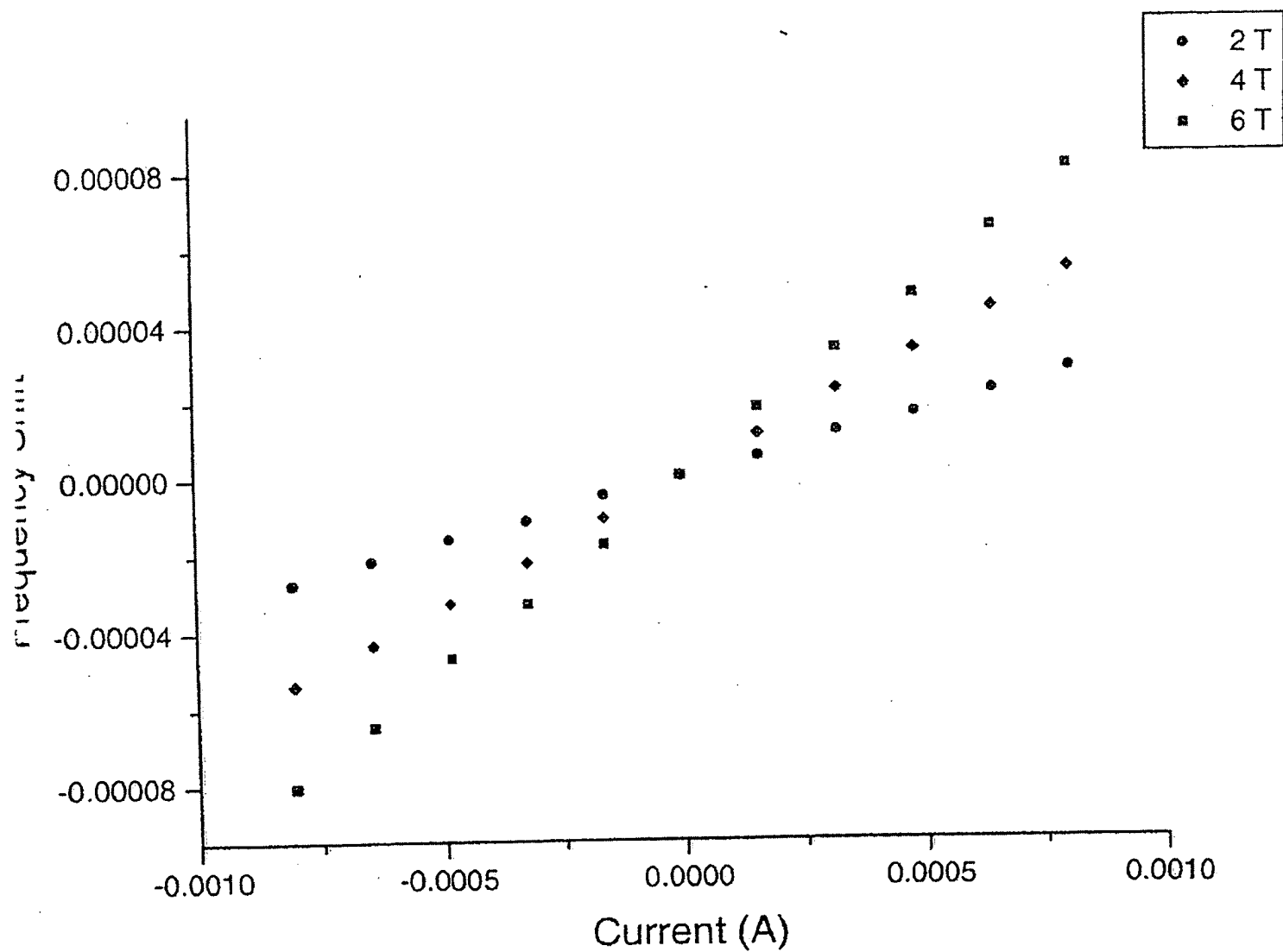


Fig. 36

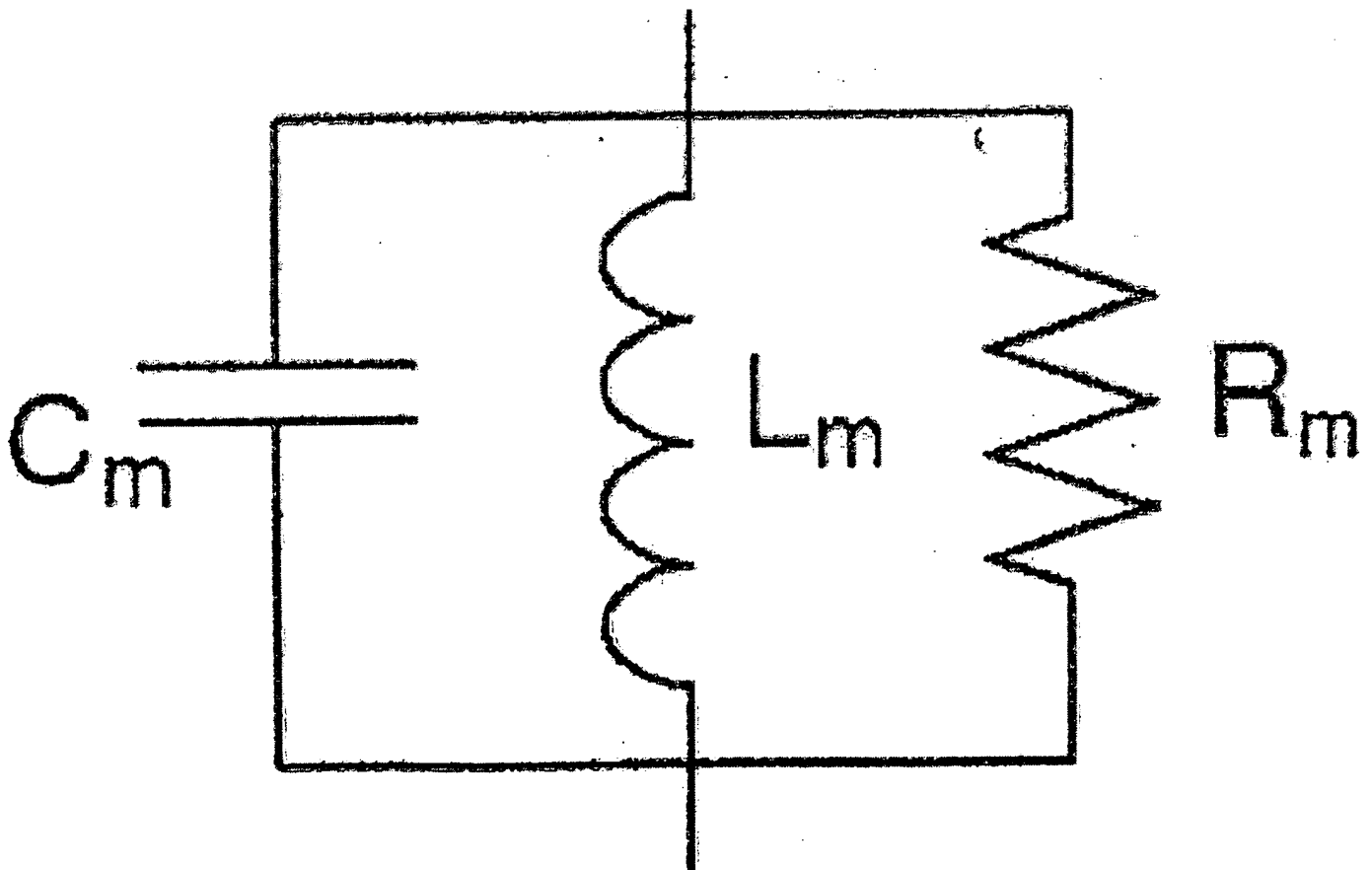


Fig. 37

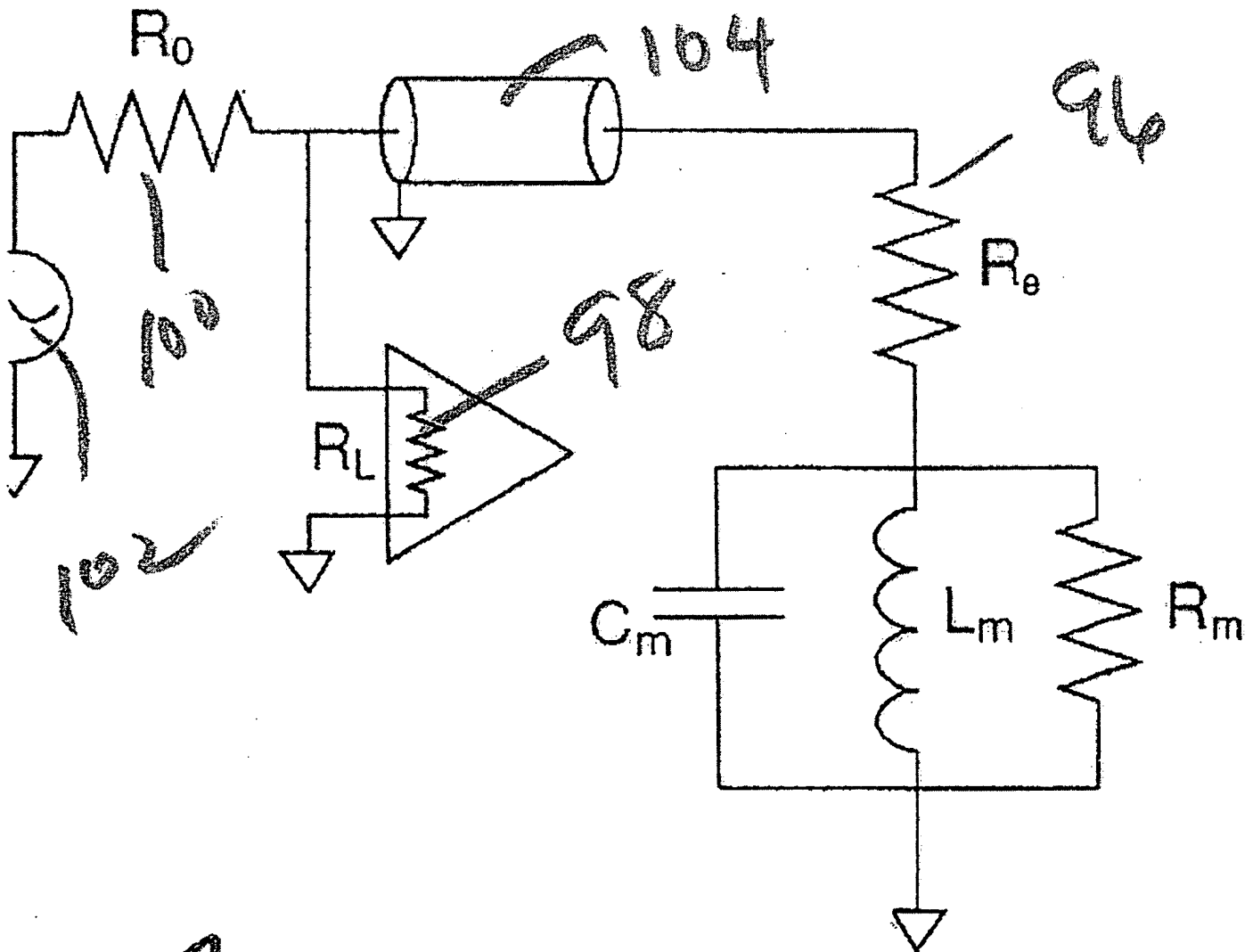


Fig. 38

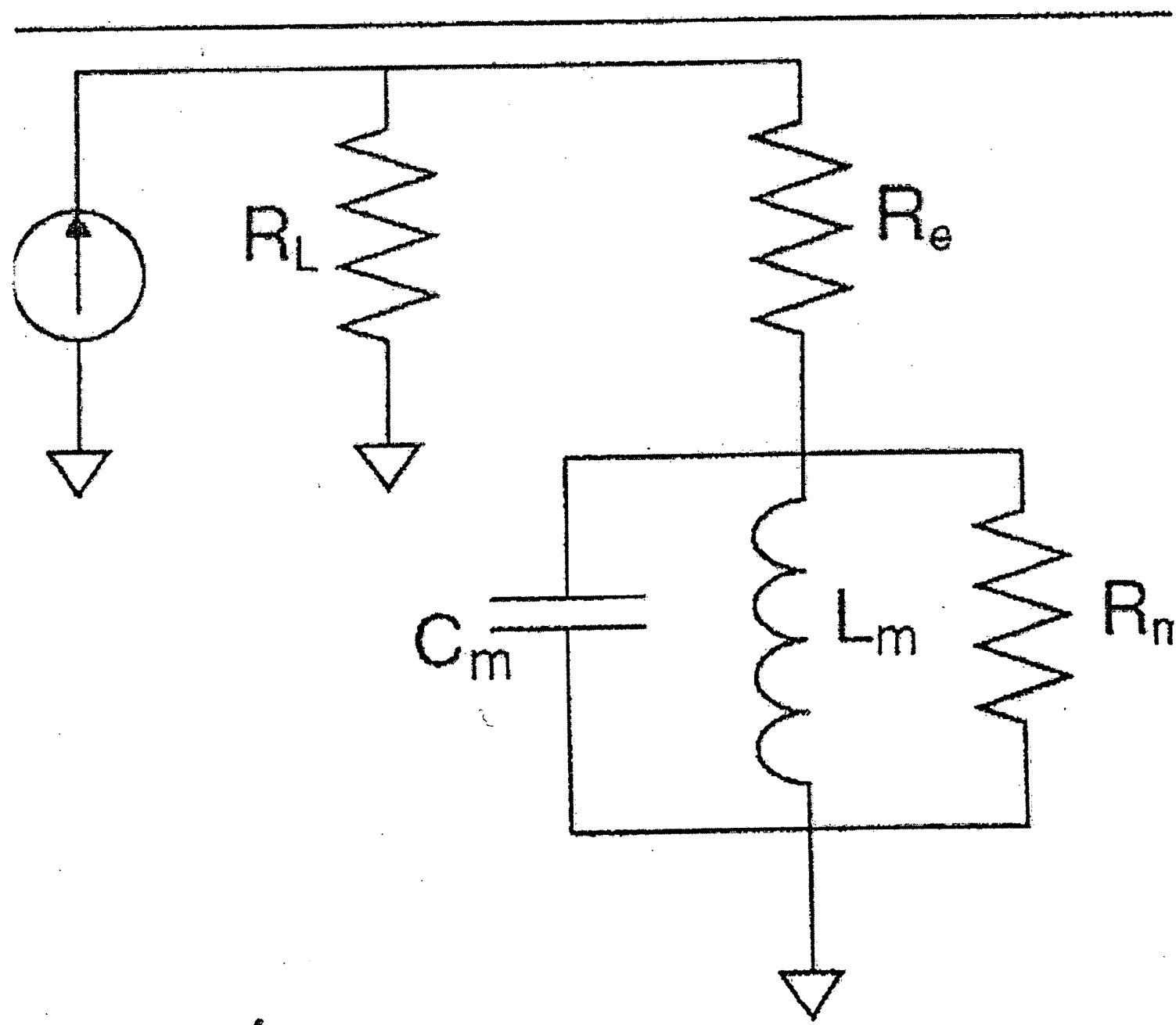


Fig. 39

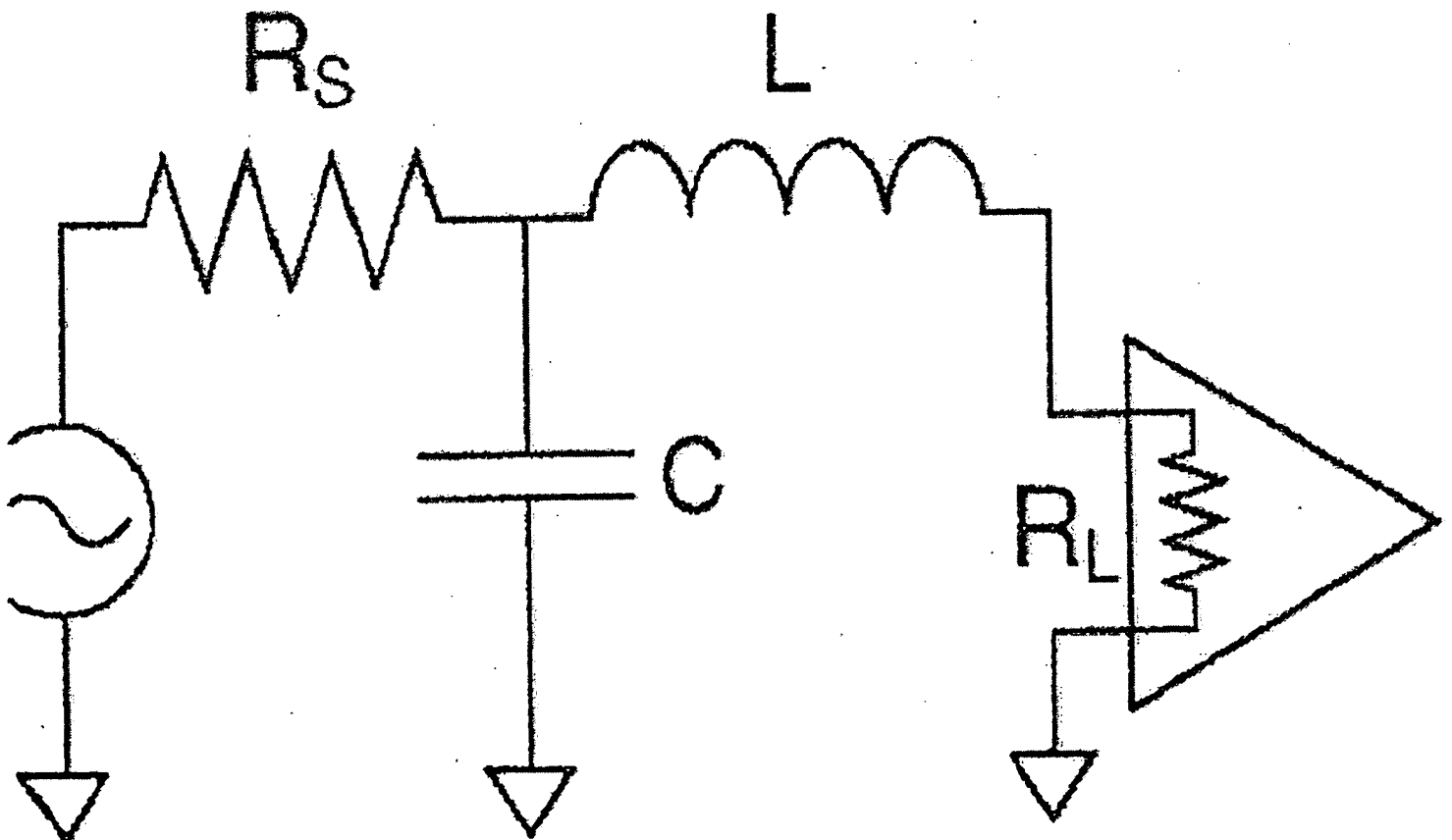


Fig. 40

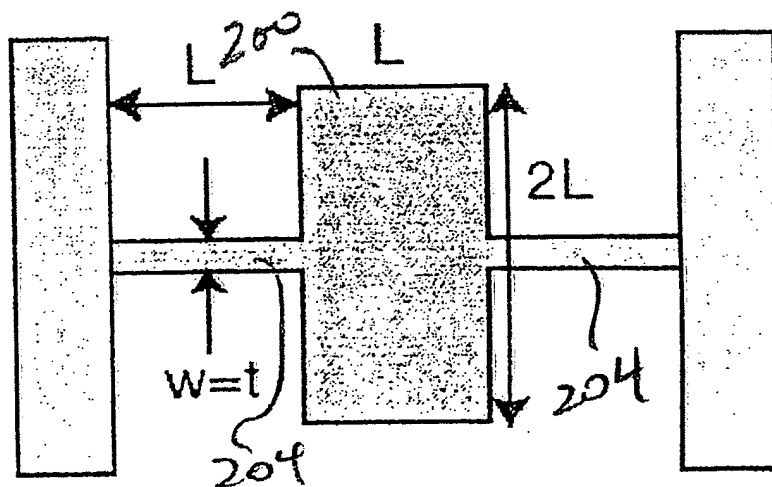
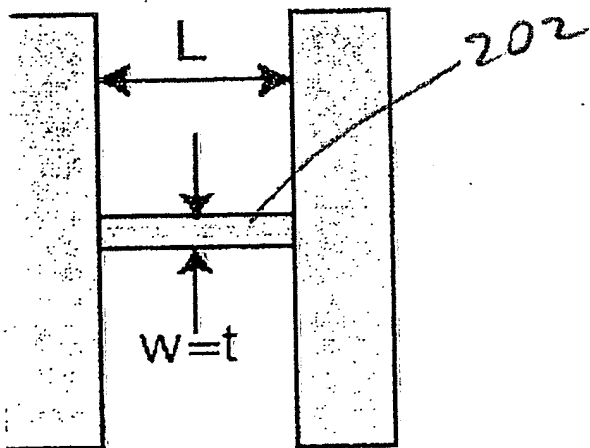


Fig. 41

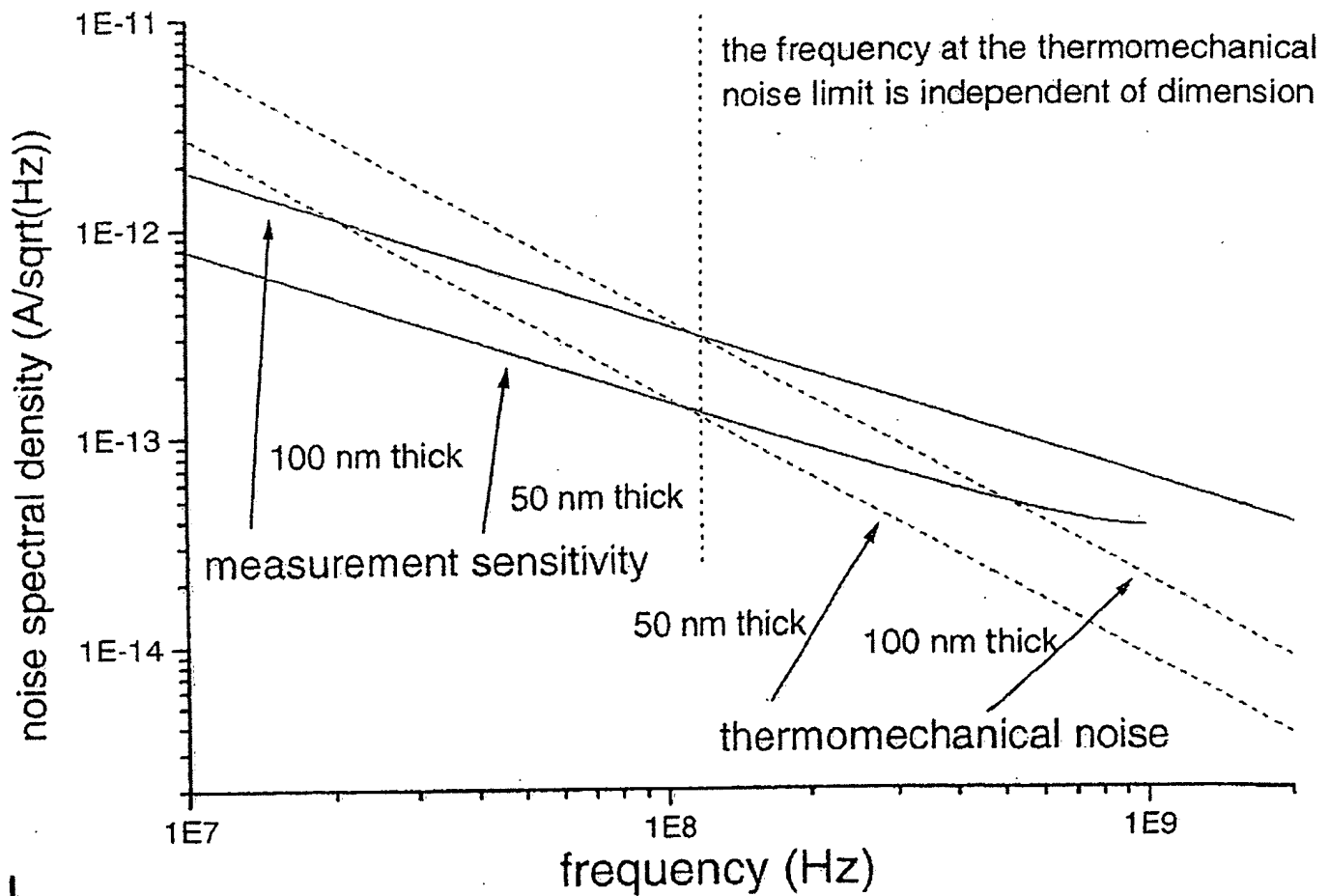


Fig. 42

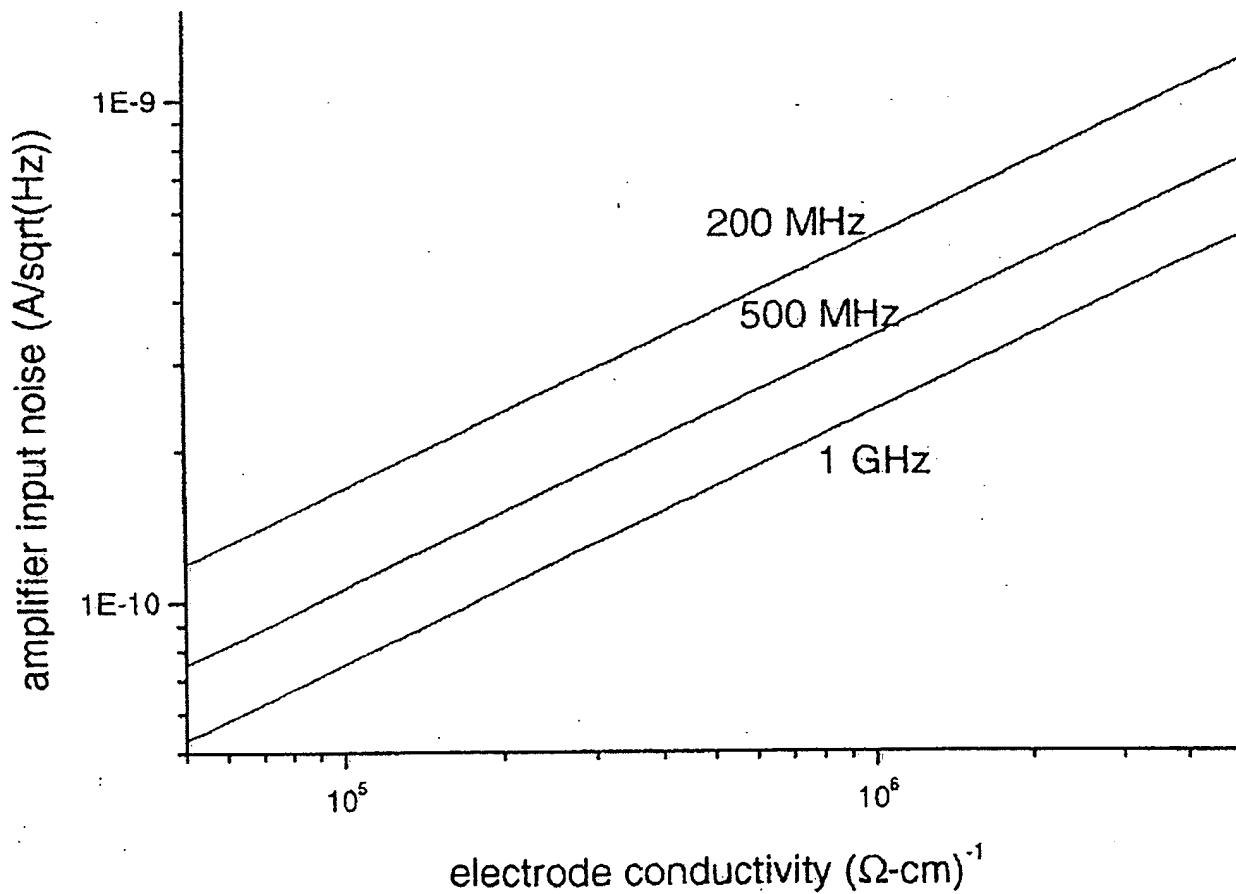


Fig. 43a

4) Initial material

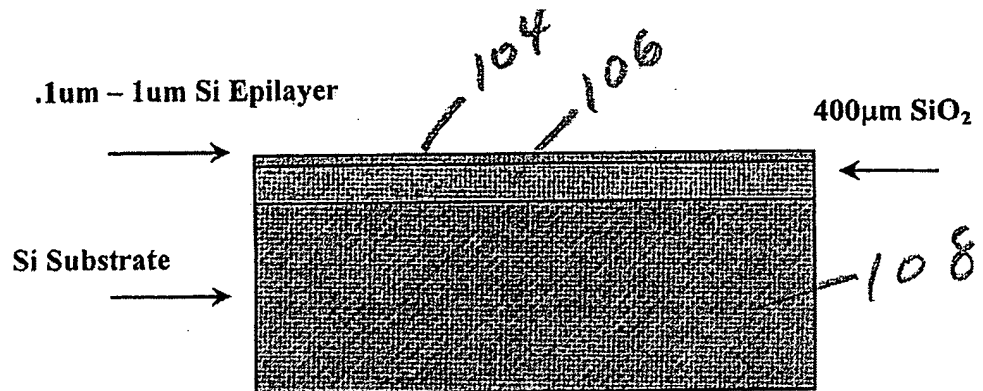


Fig. 43b

B) Masking layers and KOH etch

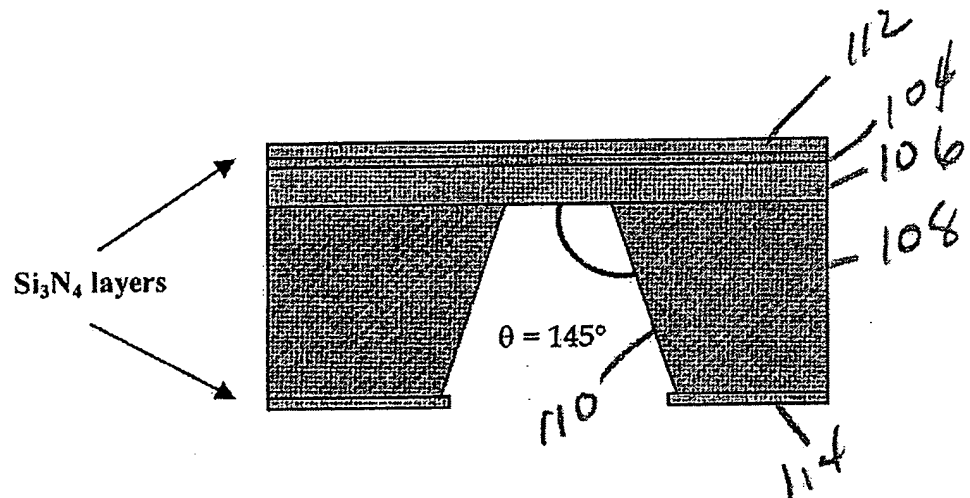
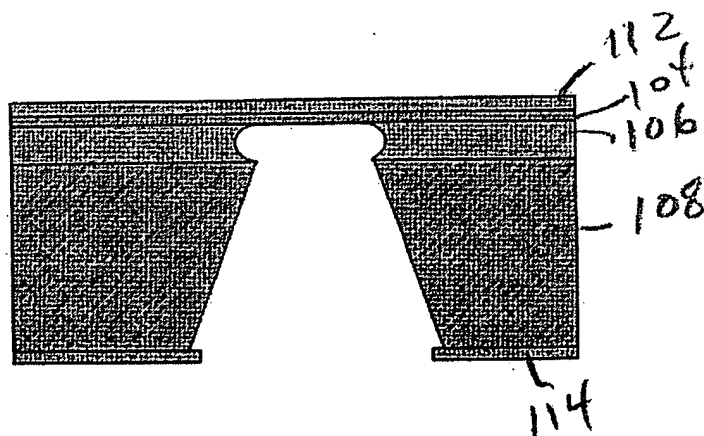
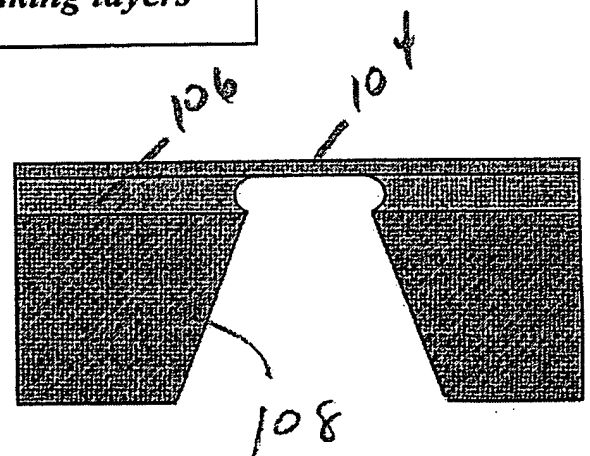


Fig. 43c

C) Removal of SiO₂ etch stop

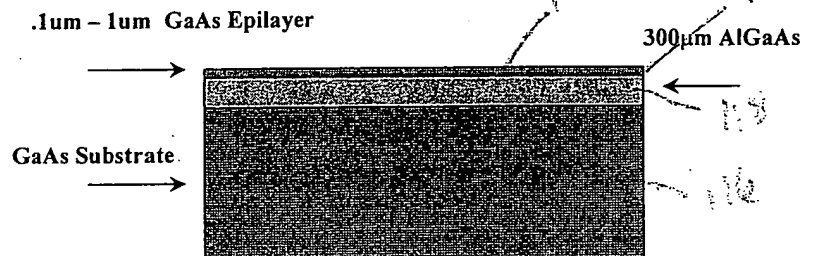


D) Removal of masking layers



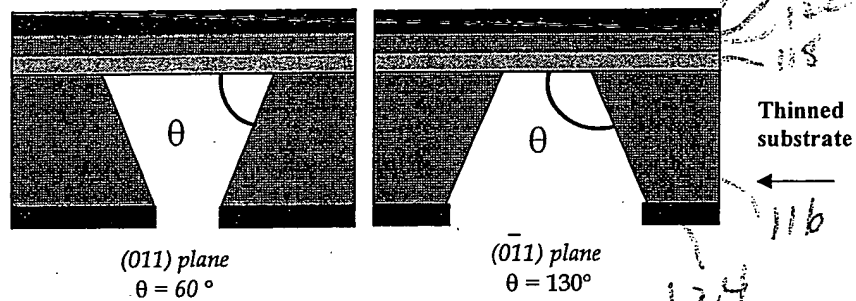
GaAs membrane process

A) Initial material

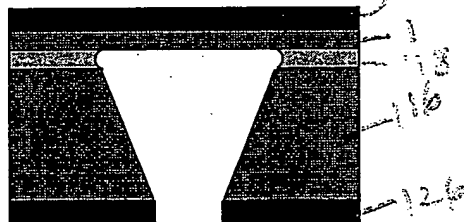


B) Masking layers and NH_4OH etch

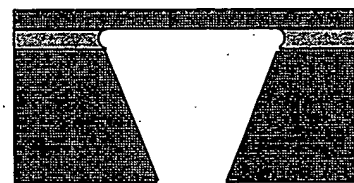
Photoresist layers



C) Removal of AlGaAs etch stop



D) Removal of masking layers



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Fig. 45

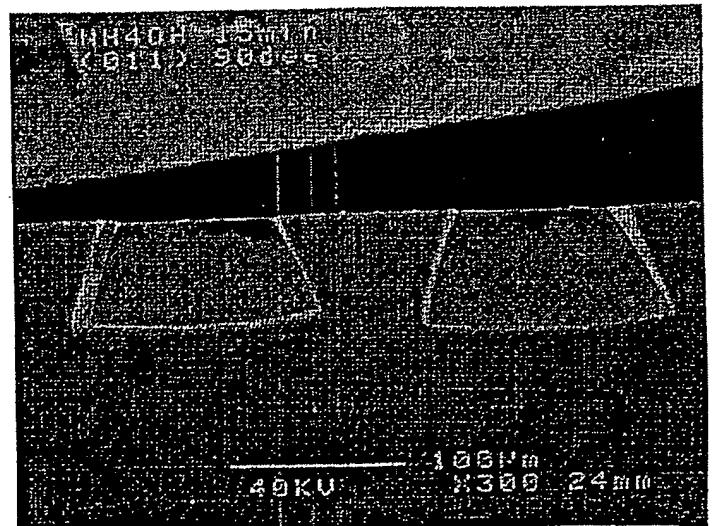
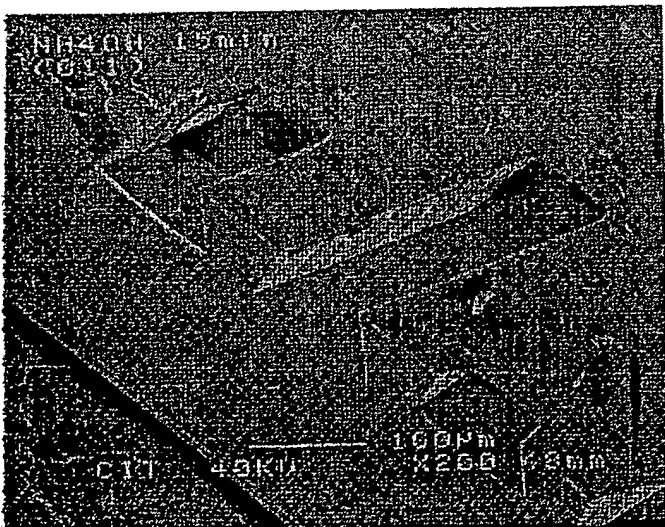


Fig. 46

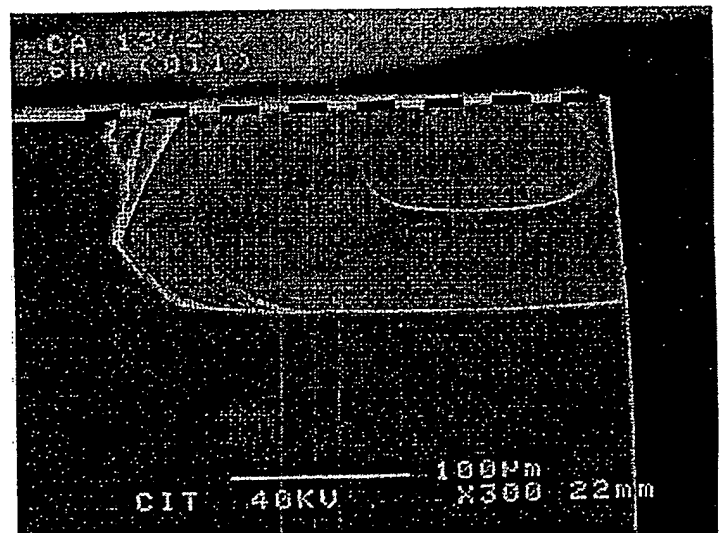
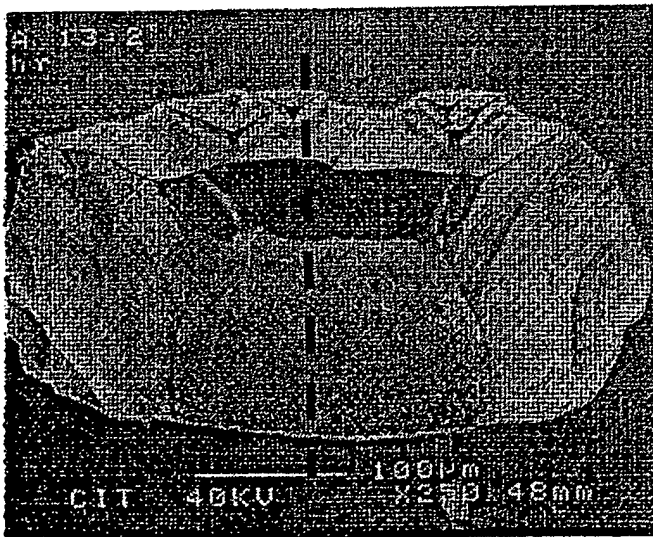


Fig. 47

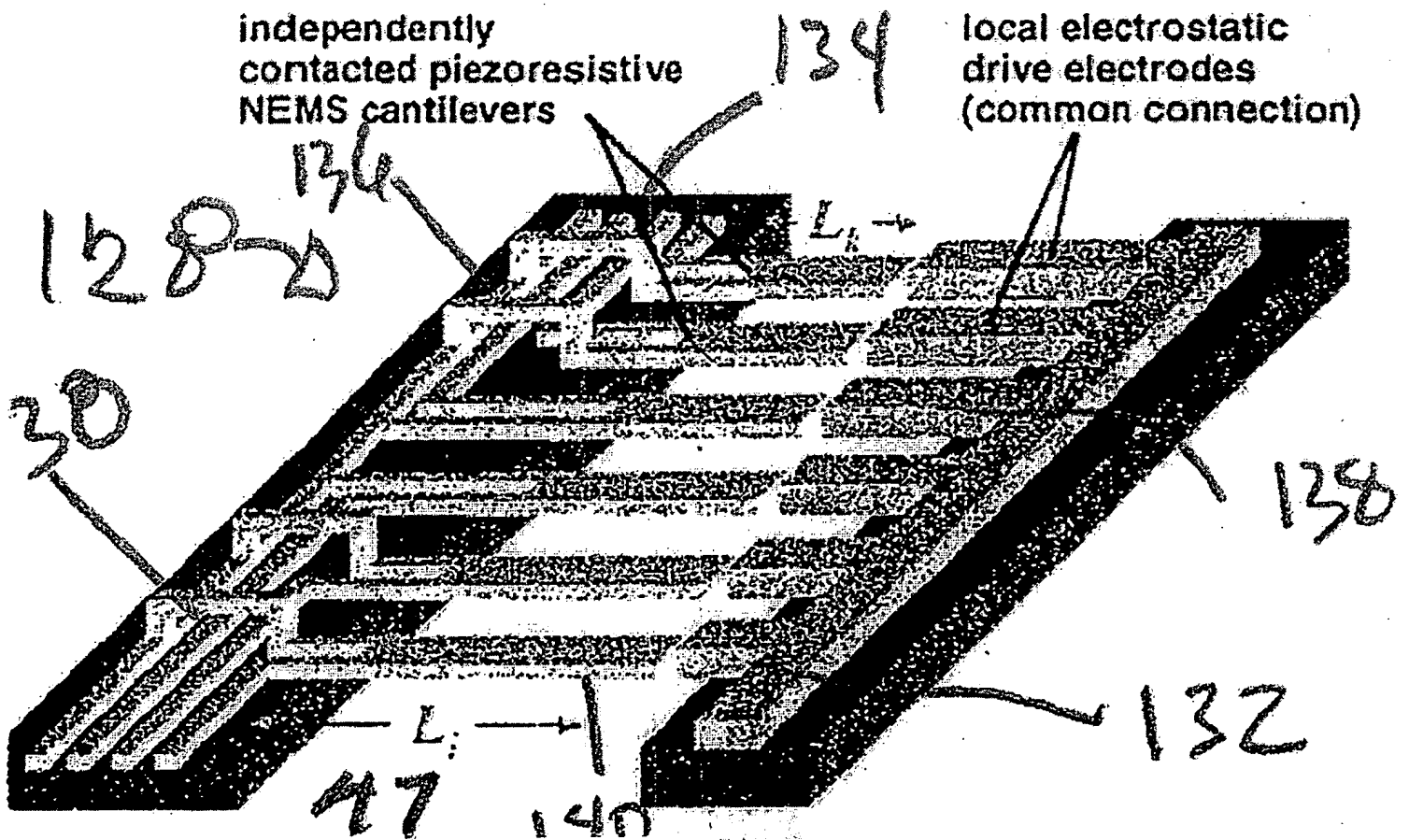


Fig. 48

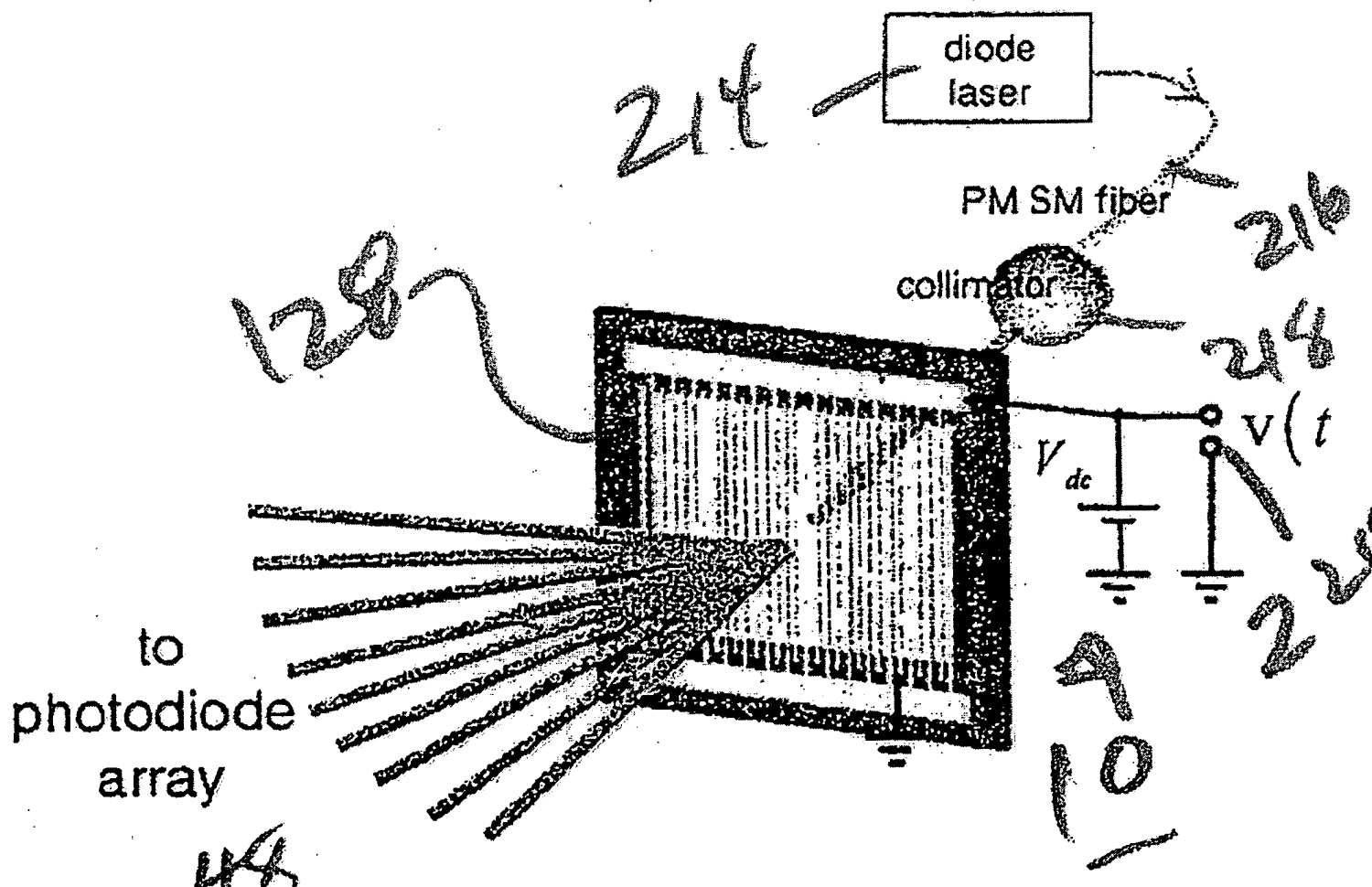


Fig. 48a

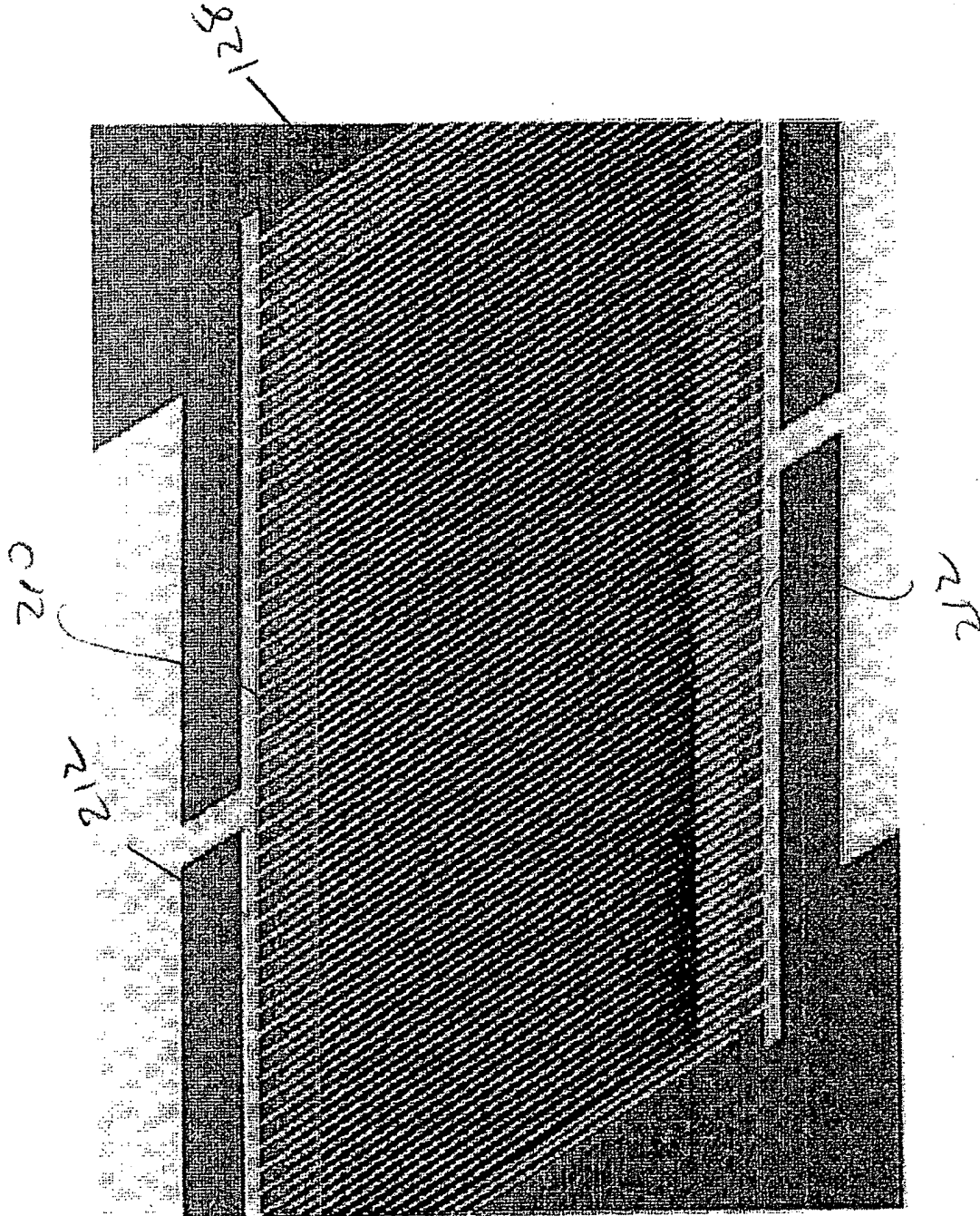


Fig. 49

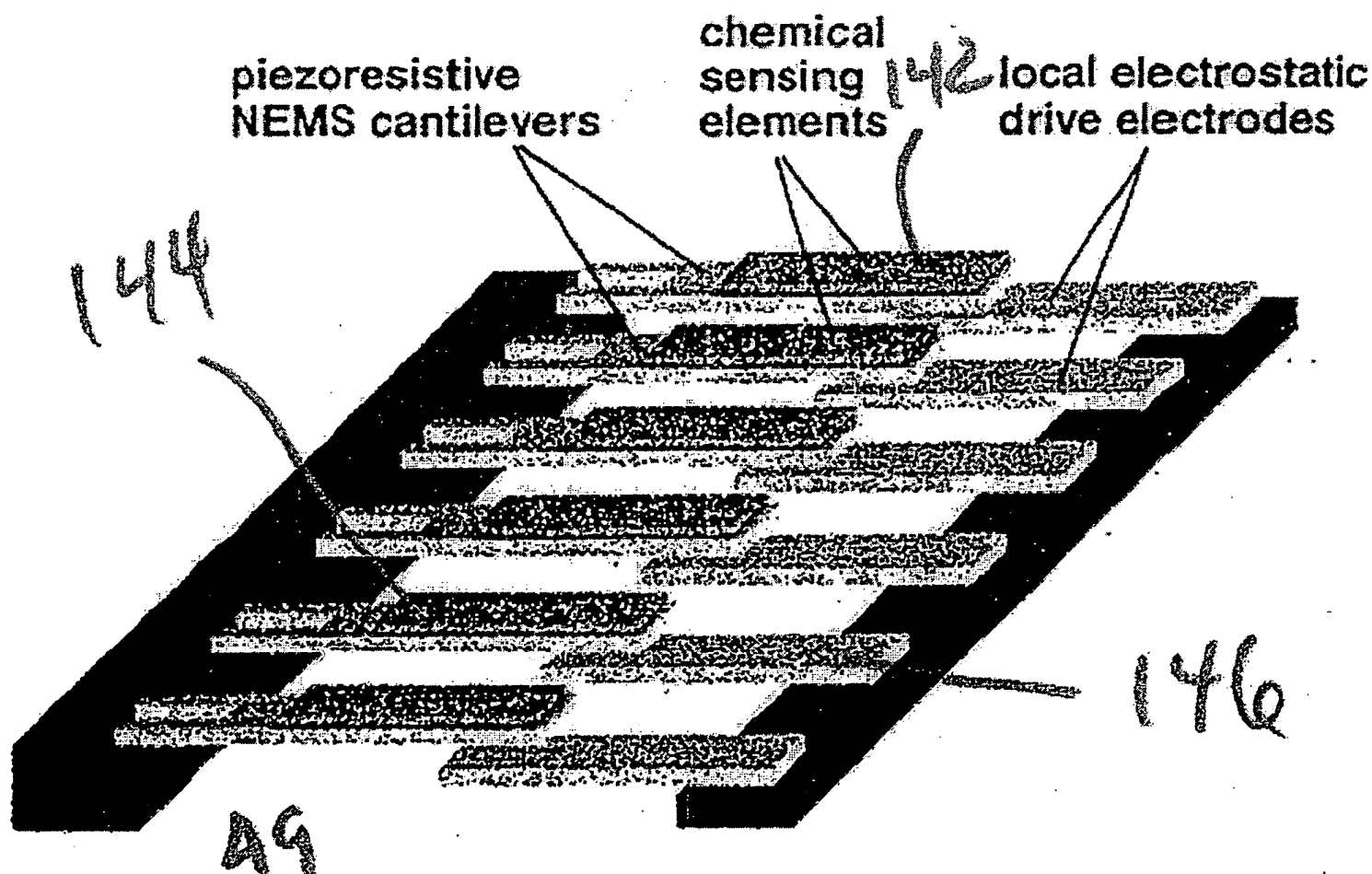
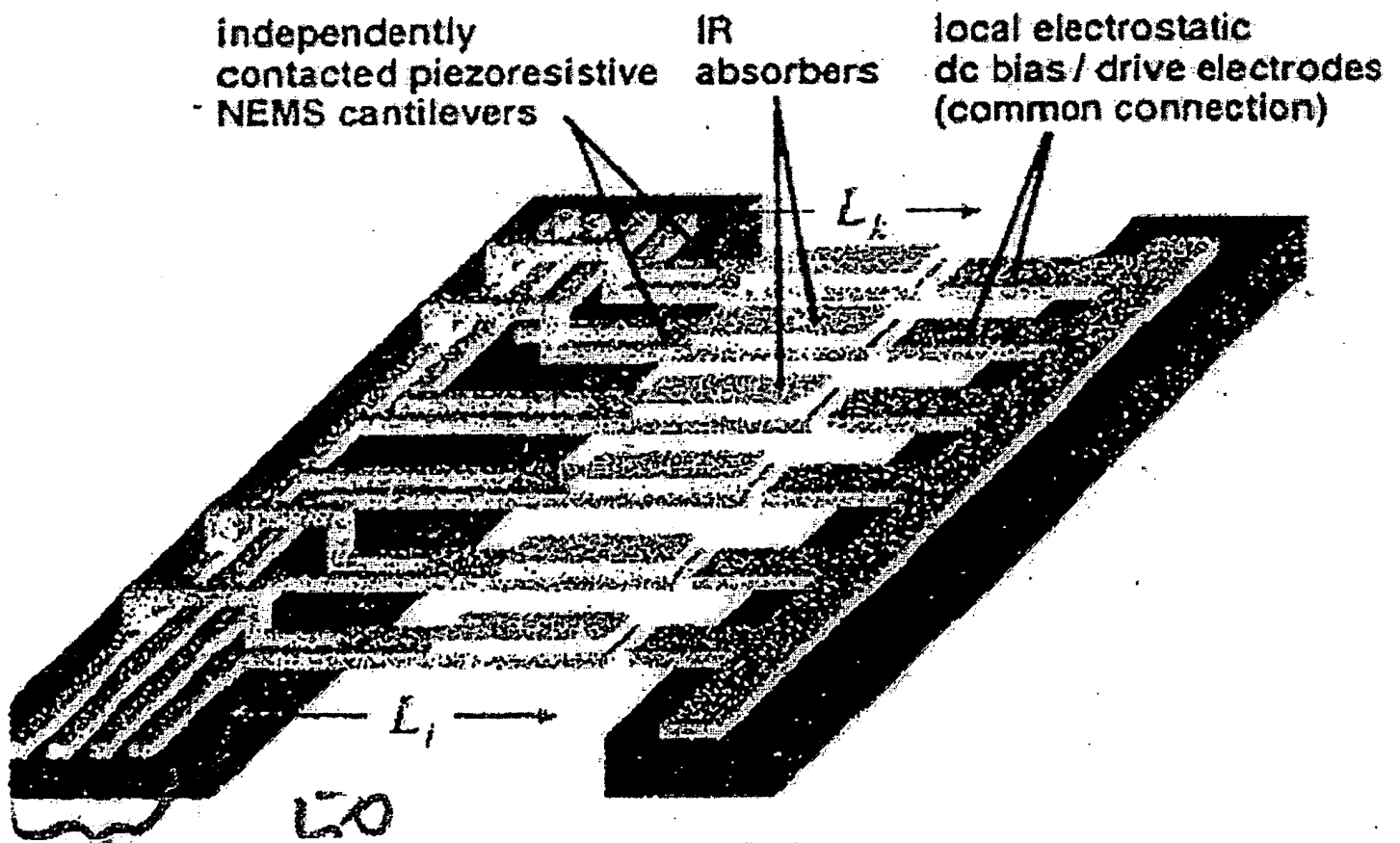
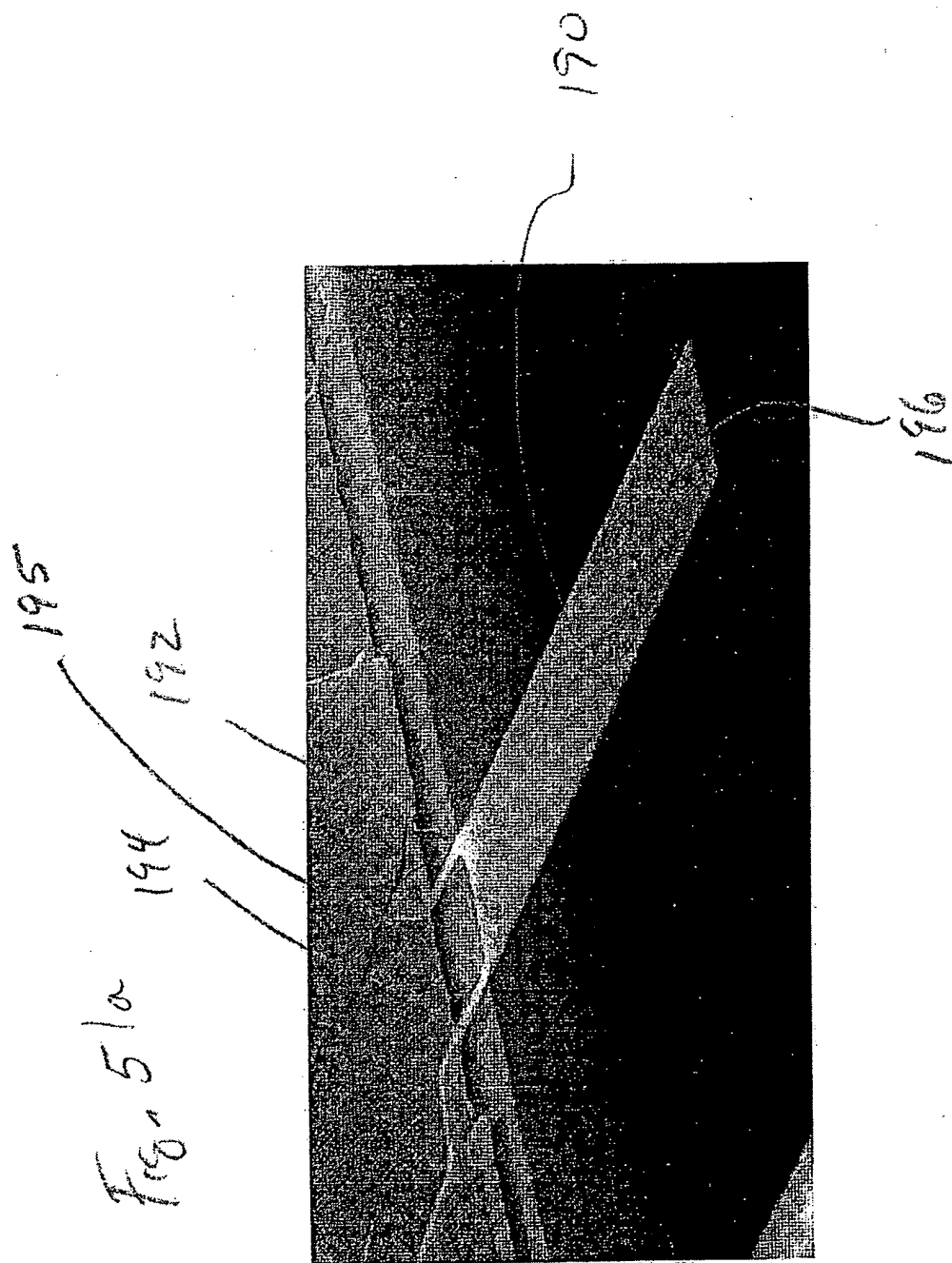


Fig. 50





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Fig. 51b

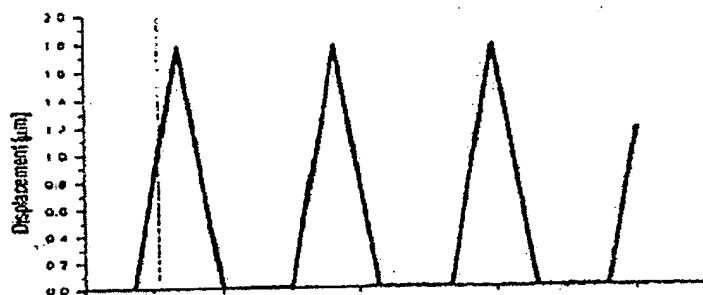


Fig. 51c

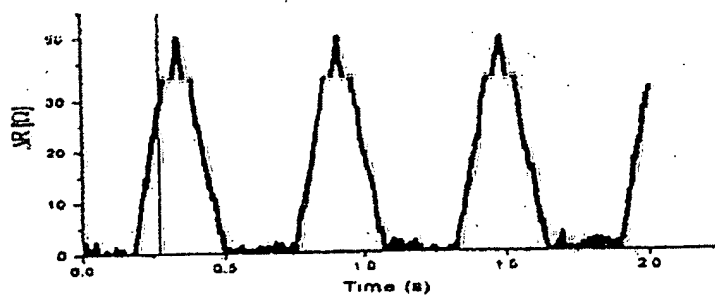


Fig. 52

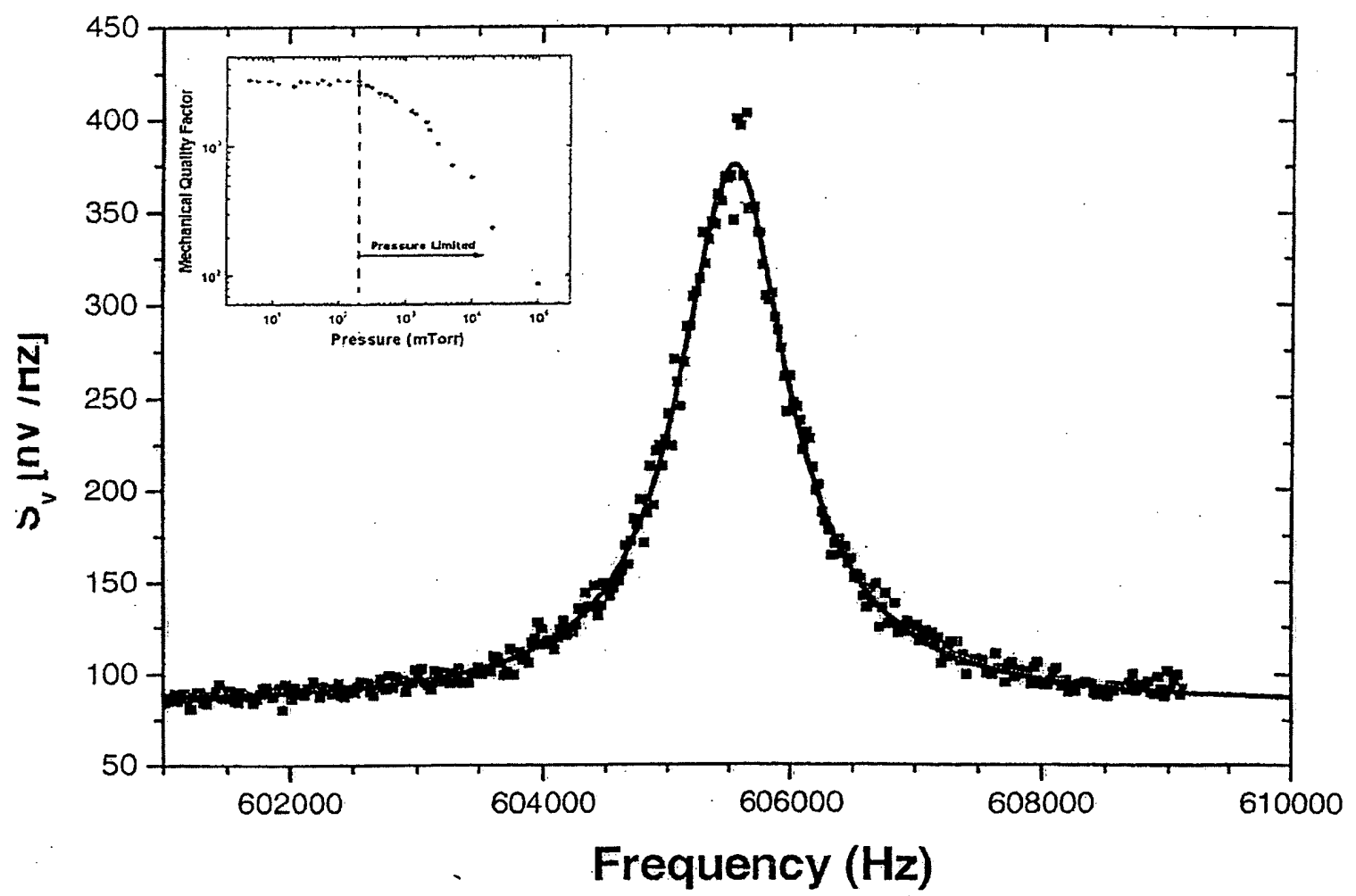


Fig. 53

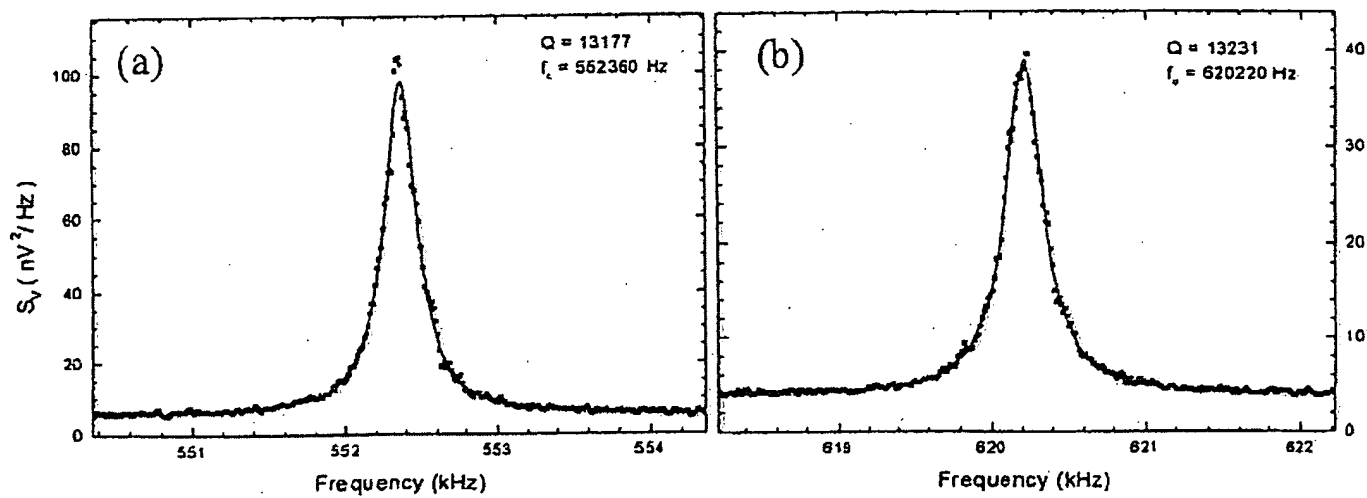


Fig. 54
19(a)

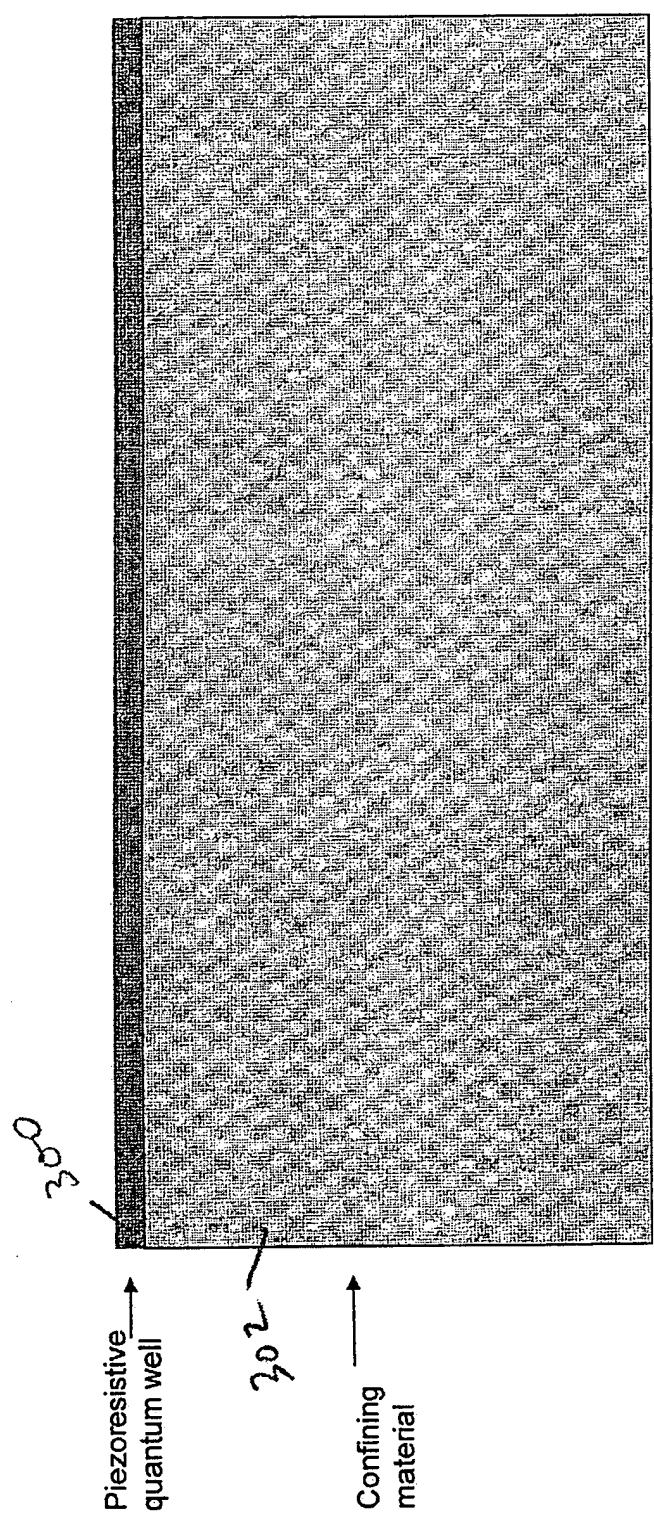


Fig. 19(b)

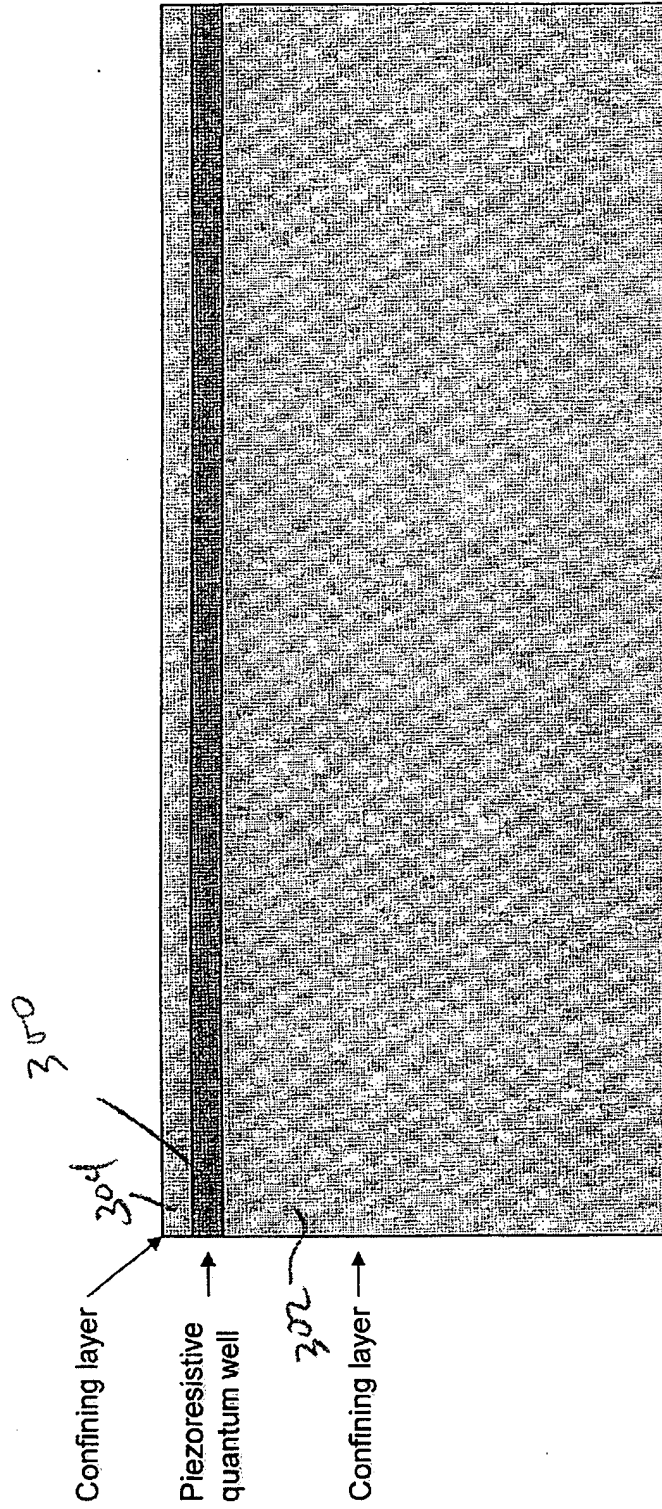
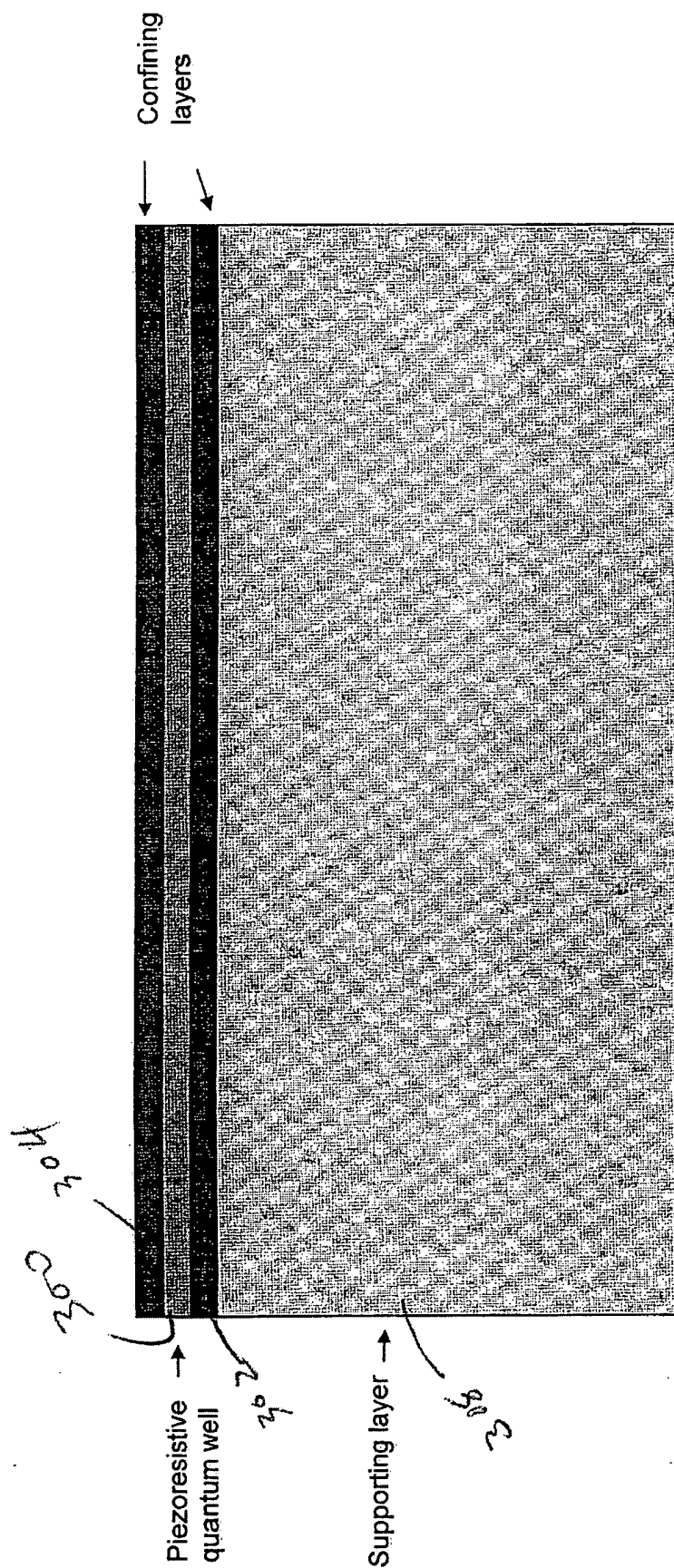
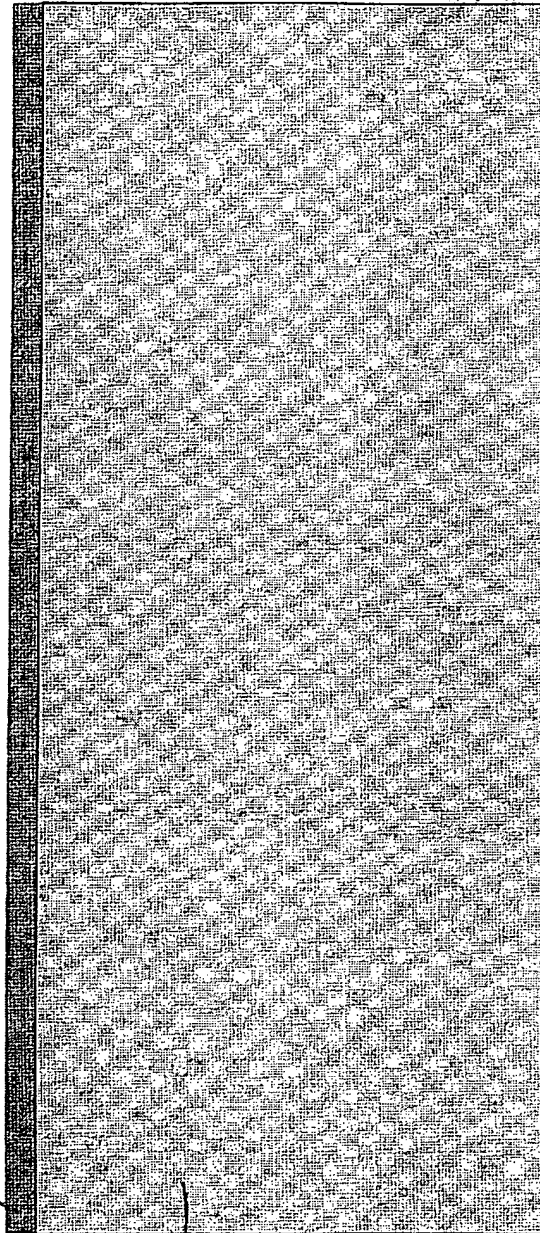


Fig. 54
FIG. 19(c)





Piezoresistive
material →

30b
↑
Insulating
material

Fig. 55

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